

Wide 2.7V to 18V V<sub>IN</sub>, 5A, High-Efficiency Bidirectional Power Backup Manager with Hot-Swap, I<sup>2</sup>C, ADC, and Capacitor Health Test

### DESCRIPTION

The MP5514 is an input power conditioning power management IC (PMIC) designed for enterprise solid-state drives (SSDs), non-volatile dual-inline memory modules (NVDIMMs), and other backup system applications. The device features input current limiting and reverse current blocking. It also integrates an MPSpatented, high-efficiency, bidirectional, buckboost converter with a single inductor for energy storage and system power backup during an input power failure. The MP5514 also provides an I<sup>2</sup>C interface and analog-to-digital converter (ADC). Users can set the input current limit (I<sub>IN\_LIMIT</sub>) and slew rate, and can perform capacitor health tests via the I2C. The MP5514 monitors system statuses, such as the input voltage (V<sub>IN</sub>), input current (I<sub>IN</sub>), storage voltage (V<sub>STRG</sub>), and temperature. It also provides interrupt options for these features.

Internal input current blocking prevents inrush current during start-up, and reverse current blocking prevents backup energy from flowing to the failing VIN port. MPS's patented energy storage and release management control circuit minimizes the storage capacitor ( $C_{\text{STRG}}$ ) requirement. The circuit increases  $V_{\text{IN}}$  to provide a higher  $V_{\text{STRG}}$  to store energy. If an input outage occurs, this energy is released to the system during a hold time ( $t_{\text{HOLD}}$ ).

The MP5514 requires a minimal number of standard external components, and is available in a QFN-30 (5mmx5mm) package.

## **FEATURES**

- MPS-Patented Bidirectional Buck-Boost Converter
- Wide 2.7V to 18V Operating Input Voltage (V<sub>IN</sub>) Range
- Up to 32V Configurable Storage Voltage (V<sub>STRG</sub>)
- Up to 6A Configurable Input Current Limit (I<sub>IN LIMIT</sub>)
- Up to 5A Buck Load Capability
- Adjustable Bus Voltage (V<sub>BUS</sub>) Slew Rate
- Input Current Limiting with Integrated 14mΩ MOSFET
- Input Over-Voltage Protection (OVP)
- Reverse-Current Protection (RCP)
- Input Power Failure Indication
- Storage Capacitor (C<sub>STRG</sub>) Health Test
- Comprehensive Voltage-, Current-, and Temperature-Sensing Analog-to-Digital Converter (ADC)
- Thermal Shutdown
- Available in a QFN-30 (5mmx5mm) Package

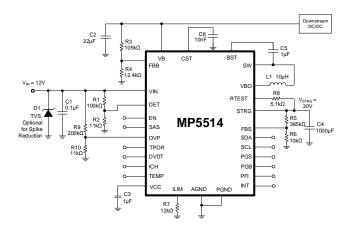
### **APPLICATIONS**

- Solid-State Drives (SSDs)
- Non-Volatile Dual-Inline Memory Modules (NVDIMMs)
- Hard-Disk Drives (HDDs)
- Power Backup Systems

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# **TYPICAL APPLICATION**



CH1: V<sub>BUS</sub>

5V/div. CH2: V<sub>STRG</sub>

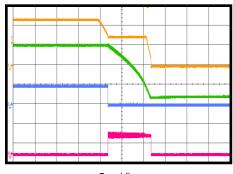
10V/div.

CH3: V<sub>PFI</sub> 5V/div.

CH4: IL

5A/div.

V<sub>STRG</sub> Release V<sub>IN</sub> = 12V, V<sub>BUS</sub> = 7.5V, I<sub>BUS\_LOAD</sub> = 5A



5ms/div.



### ORDERING INFORMATION

Part Number*	Package	Top Marking	MSL Rating
MP5514GU-xxxx	QFN-30 (5mmx5mm)	See Below	1
EVKT-5514	Evaluation Kit	-	-

<sup>\*</sup> For Tape & Reel, add suffix -Z (e.g. MP5514GU-Z).

# TOP MARKING MPSYYWW MP5514 LLLLLLL

MPS: MPS prefix YY: Year code WW: Week code MP5514: Part number LLLLLL: Lot number

# **EVALUATION KIT (EVKT-MP5514)**

EVKT-5514 kit contents (items below can be ordered separately):

#	Part Number	Item	Quantity
1	EV5514-U-00A	MP5514 evaluation board	1
2	EVKT-USBI2C-02	Includes one USB to I <sup>2</sup> C communication interface, one USB cable, and one ribbon cable	1
3	Online resources	Includes datasheet, user guide, product brief, and GUI	1

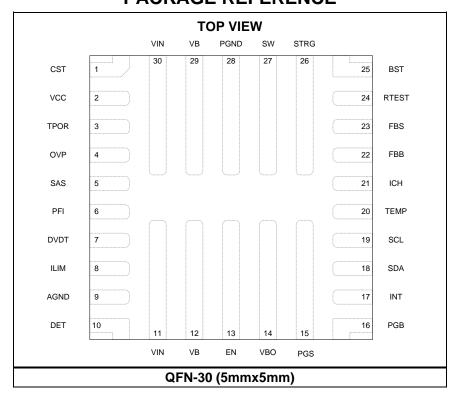
Order directly from MonolithicPower.com or our distributors.



Figure 1: EVKT-5514 Evaluation Kit Set-Up



# **PACKAGE REFERENCE**





# **PIN FUNCTIONS**

Pin #	Name	Description
1	CST	Internal charge pump storage capacitance. Connect a 10nF to 47nF capacitor between the CST and AGND pins to enable the input current limit (I <sub>IN_LIMIT</sub> ) MOSFET and the disconnect MOSFET.
2	VCC	Internal LDO output. The VCC pin provides power to the internal circuitry. Decouple VCC using a ≥1µF ceramic decoupling capacitor, placed as close to VCC as possible. Do not add an external load to VCC.
3	TPOR	Start-up reset delay. Connect a ≥1nF capacitor between the TPOR and AGND pins to set the start-up reset delay time (ttpor). Float TPOR for the default ttpor (1.5ms).
4	OVP	<b>Over-voltage protection.</b> A resistor divider connected between the VIN and OVP pins configures the input over-voltage protection (OVP) threshold ( $V_{IN\_OVP}$ ). If $V_{IN\_OVP}$ exceeds 0.81V, then the MP5514 enters buck release mode. If $V_{IN\_OVP}$ drops below 0.765V, and the VB pin triggers the bus voltage ( $V_{BUS}$ ) under-voltage lockout (UVLO) protection, then the part recovers as the first start-up in default with a new $t_{TPOR}$ . Connect the OVP to AGND pins if the OVP function is not used.
5	SAS	Configured SAS function. Pull the SAS pin high to turn off the $I_{\text{IN\_LIMIT}}$ MOSFET and have the part operate in backup mode. If $V_{\text{BUS}}$ drops below its UVLO threshold ( $V_{\text{BUS\_UVLO}}$ ), then the part exits buck release mode. The internal LDO continues operating. SAS is pulled down internally via a $4\text{M}\Omega$ resistor.
6	PFI	<b>Power failure indication.</b> The PFI pin is an open-drain output. Pull PFI up to a power source via a resistor to enable the power failure indication function. If the DET voltage (V <sub>DET</sub> ) exceeds 1.02 x the V <sub>DET</sub> reference voltage (V <sub>DET_REF</sub> ), then PFI is pulled high. If V <sub>DET</sub> drops below 0.99 x V <sub>DET_REF</sub> , then PFI is pulled low. Once PFI is pulled low, it remains low for a blanking time (200µs). If SAS, OTP, or EN is off, then PFI is pulled low. If EN is low, then PFI is pulled low, regardless of whether PFI is pulled up to an external DC source. If both VIN and VCC are not available, then PFI is pulled to about 0.85V.
7	DVDT	Bus voltage start-up slew rate control. Connect a capacitor $\geq 1$ nF between the DVDT and AGND pins to configure the V <sub>BUS</sub> start-up slew rate. Float DVDT to control the DVDT time (t <sub>DVDT</sub> ) via the I <sup>2</sup> C.
8	ILIM	<b>DC input current limit.</b> Connect a resistor between the ILIM and AGND pins to adjust the DC current limit (I <sub>LIMIT</sub> ) between the VIN and VB pins. Apply >1.5V to ILIM to trigger overcurrent protection (OCP) and to disable the isolation MOSFET between VIN and VB.
9	AGND	IC signal ground.
10	DET	Input voltage detection. The DET pin sets the buck release voltage (VBUCK_RLS) once the input voltage (VIN) drops until VDET below 0.99 x VDET_REF.
11, 30	VIN	Input supply voltage. Place a 0.1μF ceramic capacitor as close to the VIN pin as possible. If the VIN power line is long and the system has a high V <sub>IN</sub> spike, then place a TVS diode at the input. See the Selecting the Input Capacitor and TVS Diode section on page 43 for more details.
12, 29	VB	Bus voltage. Place a 22μF to 47μF ceramic capacitor as close to the VB pin as possible.
13	EN	<b>Enable.</b> The EN pin enables and disables the internal circuitry. Pull EN low to have the part operate in buck release mode until the storage voltage ( $V_{STRG}$ ) is discharged. The IC shuts down once $V_{BUS}$ drops and EN is pulled down internally via a $4M\Omega$ resistor. EN has a higher sink current if >2V are applied to it.
14	VBO	<b>Internal disconnect MOSFET source.</b> Connect an inductor between the SW and VBO pins for backup boost charge mode and buck release mode.



# PIN FUNCTIONS (continued)

Pin#	Name	Description
15	PGS	Storage voltage power good indication. The PGS threshold bits (register 06h, bits[3:0]) are set to 1111 by default. If the FBS voltage (V <sub>FBS</sub> ) exceeds 0.97 x the V <sub>FBS</sub> reference voltage (V <sub>FBS_REF</sub> ), the then PGS pin is pulled high. If V <sub>FBS</sub> drops below 0.95 x V <sub>FBS_REF</sub> , then PGS is pulled low. PGS can be configured via register 06h. PGS is driven by an internal circuit, and does not require an external pull-up resistor. PGS is low, regardless of whether the IC is enabled or disabled. If power from both VIN and VCC are not available, then PGS is pulled down to about 1.3V.
16	PGB	Bus voltage power good indication. If the FBB voltage ( $V_{FBB}$ ) exceeds 0.95 x the $V_{FBB}$ reference voltage ( $V_{FBB,REF}$ ), then PGB is pulled high. If $V_{FBB}$ drops below 0.9 x $V_{FBB,REF}$ , then PGB is pulled low. PGB is driven by an internal circuit, and does not require an external pull-up resistor. PGB is low, regardless of whether the IC is enabled or disabled. If power from both VIN and VCC are not available, then PGB is pulled down to about 1.3V.
17	INT	Interrupt output. The INT is an open-drain output. Even if INT is pulled up to external DC source, INT is pulled low when If EN is low and the IC is not in buck release mode, then INT is pulled low, regardless of whether the part is enabled or disabled. If both VIN and VCC are not available, INT is pulled down to about 0.85V.
18	SDA	I <sup>2</sup> C serial data.
19	SCL	I <sup>2</sup> C serial clock.
20	TEMP	Temperature sense input from thermistor to ADC.
21	ICH	<b>Boost charge mode configurable peak switching current.</b> Float the ICH pin to set the boost charge mode peak switching current to 2A.
22	FBB	Bus voltage feedback sense. The FBB pin regulates V <sub>BUS</sub> in buck release mode.
23	FBS	Storage voltage feedback sense. The FBS pin sets the V <sub>STRG</sub> in boost charge mode.
24	RTEST	Resistor connection for the capacitor health test. During a storage capacitor (CSTRG) health test, the RTEST pin is pulled to PGND internally. A resistor connected between the STRG and RTEST pins discharges CSTRG. The RTEST discharge current (IRTEST) should be below 500mA.
25	BST	<b>Bootstrap.</b> Connect a bootstrap capacitor (C <sub>BST</sub> ) between the BST and SW pins to supply the high-side MOSFET (HS-FET) driver.
26	STRG	<b>Backup energy storage.</b> Connect C <sub>STRG</sub> to the STRG pin for the energy storage and release functions.
27	SW	<b>Switch output.</b> The SW pin is used for the energy storage and release circuitry. Connect an inductor between the SW and VBO pins.
28	PGND	Power ground.



# ABSOLUTE MAXIMUM RATINGS (1) Input voltage (V<sub>IN</sub>)......21V V<sub>B</sub>, V<sub>BO</sub>.....-0.3V to +21V V<sub>STRG</sub>, V<sub>RTEST</sub>.....-0.3V to +36V $V_{SW}$ .......... -0.3V (-6V for <10ns) to $V_{STRG}$ + 0.3V $V_{BST}$ .....-0.3V to $V_{STRG}$ + 6V V<sub>CST</sub> .....-0.3V to +28V All other pins.....-0.3V to +6V Continuous power dissipation (T<sub>A</sub> = 25°C) (4) ......3.57W Junction temperature ...... 150°C Storage temperature .....-65°C to +150°C ESD Ratings Human body model (HBM) .....2000V Charged device model (CDM)......750V Recommended Operating Conditions (5) Input voltage (V<sub>IN</sub>)......2.7V <sup>(6)</sup> to 18V Bus voltage (V<sub>BUS</sub>) ...... 2.6V to 16V Storage voltage (V<sub>STRG</sub>)......V<sub>IN MAX</sub> + 3V to 32V Max input current (I<sub>IN MAX</sub>) ......6A Max buck release mode current (IBUCK RLS).....5A Operating junction temp (T<sub>J</sub>)....-40°C to +125°C

Thermal Resistance	$oldsymbol{ heta}_{JA}$	$\boldsymbol{\theta}$ JC	
QFN-30 (5mmx5mm)			
EV5514-U-00A (7)	35	6.5	°C/W
JESD51-7 <sup>(8)</sup>	36	8	°C/W

### Notes:

- 1) Exceeding these ratings may damage the device.
- For more details, see the Enable (EN) Control section on page
- If these pins are pulled up to a power source, then the current should be below the maximum value.
- 4) The maximum allowable power dissipation is a function of the maximum junction temperature  $T_J$  (MAX), the junction-to-ambient thermal resistance  $\theta_{JA}$ , and the ambient temperature  $T_A$ . The maximum allowable continuous power dissipation at any ambient temperature is calculated by  $P_D$  (MAX) =  $(T_J (MAX) T_A) / \theta_{JA}$ . Exceeding the maximum allowable power dissipation can cause excessive die temperature, which may cause the device to go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- 6) Guaranteed for temperatures conditions ≥25°C. If the temperature drops below 25°C, then it is recommended to connect a Schottky diode between the VIN and VCC pins for start-up from a 2.7V input.
- 7) Measured on EV5514-U-00A (63mmx63mm), 2-layer PCB.
- B) Measured on JESD51-7, 4-layer PCB.



# **ELECTRICAL CHARACTERISTICS**

 $V_{IN}$  = 12V,  $V_{EN}$  = 2V,  $T_J$  = -40°C to 125°C  $^{(9)}$ , typical value is tested at  $T_J$  = 25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units
Power Supply						
Shutdown current	I <sub>SD</sub>	$V_{EN} = 0V$ , then VIN starts up, $T_J = 25$ °C		2.5	5	μΑ
Quiescent current	Ιq	V <sub>SAS</sub> = 2V, V <sub>EN</sub> = 2V, V <sub>FBB</sub> = V <sub>FBS</sub> = V <sub>DET</sub> = 1.1V		1.5		mA
Quiescent current	Vsas = 0V, Ven = 2V, Vfbb = Vfbs = VDet = 1.1V			2.5	3	mA
VCC regulator voltage	Vcc	VIN or VBUS = 6V, IVCC = 1mA	4.75	5	5.25	V
Input voltage (V <sub>IN</sub> ) undervoltage lockout (UVLO) rising threshold (10)	V <sub>IN_UVLO_</sub> RISING	EFUSE_UVLO = 00		2.5		V
V <sub>IN</sub> UVLO falling threshold	VIN_UVLO_ FALLING	EFUSE_UVLO = 00		2.3		V
VIN to VB current-limit MOSFET on resistance	RDS(ON)_CLM			14		mΩ
VIN to VB continuous	h	$R_{ILIM} = 36.5k\Omega$ , $T_J = 25$ °C	1.9	2	2.1	Α
current limit (ILIMIT) warning	ILIMIT_WRN	$R_{ILIM} = 36.5 k\Omega$ , $T_J = -40$ °C to $125$ °C (9)	1.84	2	2.16	Α
Shutdown leakage current	I <sub>SD_LKG</sub>	$V_{IN}$ = 12V and $V_{BUS}$ = 0V, or $V_{BUS}$ = 12V and $V_{IN}$ = 0V; $T_J$ = 25°C		2	3	μA
VB clamping voltage	VCLAMP	V <sub>IN</sub> = 18V	15.2	16	16.8	V
Bus voltage (V <sub>BUS</sub> ) rise time (DVDT) (11)	t <sub>DVDT</sub>	DVDT is floating, V <sub>IN</sub> = 12V, DVDT bits = 00, t <sub>DVDT</sub> test		1.6		ms
DVDT current	I <sub>DVDT</sub>	Connect a capacitor to DVDT,  IDVDT test		3		μΑ
Internal reset delay time	tDELAY	TPOR is floating, toelay test		1.5		ms
TPOR current	I <sub>TPOR</sub>	Connect a capacitor to TPOR, ITPOR test		1		μΑ
<b>Energy Storage and Relea</b>	se					
Storage pre-charge current	IPRE-CHARGE		250	350	450	mA
Boost disconnect MOSFET on resistance	R <sub>DS(ON)_DIS</sub>			30		mΩ
Boost charge mode peak	I <sub>CH</sub>	ICH is floating, L = 10μH		2		Α
switching current	iCH	$R_{ICH} = 200k\Omega$ , L = $10\mu$ H		0.65		Α
Energy management high- side MOSFET (HS-FET) on resistance	R <sub>DS(ON)_</sub> HS			80		mΩ
Energy management low- side MOSFET (LS-FET) on resistance	Rds(ON)_Ls			40		mΩ
FBB feedback voltage	Vens	T <sub>J</sub> = 25°C	0.792	8.0	0.808	V
T DD TEEUDACK VOITAGE	V <sub>FBB_REF</sub>	$T_J = -40$ °C to 125°C	0.786	0.8	0.812	V
	M	T <sub>J</sub> = 25°C	0.792	0.8	0.808	V
FBS feedback voltage	V <sub>FBS_REF</sub>	T <sub>J</sub> = -40°C to 125°C	0.786	0.8	0.812	V
DET G. Albertone	1/	T <sub>J</sub> = 25°C	0.792	0.8	0.808	V
DET feedback voltage	$V_{DET\_REF}$	T <sub>J</sub> = -40°C to 125°C	0.786	0.8	0.812	V



# **ELECTRICAL CHARACTERISTICS** (continued)

 $V_{IN}$  = 12V,  $V_{EN}$  = 2V,  $T_J$  = -40°C to 125°C (9), typical value is tested at  $T_J$  = 25°C, unless otherwise noted.

FBB feedback current  FBS feedback current  FBS feedback current  IFBS  FBS feedback current  IFBS  FBS Feedback current  IDET  FBS VFBS = VFBS = VDET = 0.85V  VFBB = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBB = VFBS = VDET = 0.85V  VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VFBS = VDET = 0.85V  VFBS = 0.85V  VFBS = VFBS = VDET = 0.85V  VFBS = VFBS = VBS = 0.85V  VFBS = VFBS = VFBS = VBS = 0.85V  VFBS = VFBS = VBS = 0.85V  VFBS = VFBS = VBS		10 10 10 0.81 45	50 50 50	nA nA nA V
DET feedback current  Vin over-voltage protection (OVP) threshold  Vin_OVP bysteresis  Vin_OVP_Hysteresis  Vin_OVP_Hysteresis  Vin_ovP_Hysteresis  Vin_ovP_Hysteresis  Vin_ovP bysteresis		10 0.81 45		nA V
VIN over-voltage protection (OVP) threshold  VIN_OVP hysteresis  VIN_OVP_HYS  VIN_OVP hysteresis  VSTRG_OVP  VIN to VB isolation MOSFET start-up voltage  VIN to VB isolation MOSFET shutdown current  PFI high voltage threshold  VPFI_HIGH  PFI low voltage threshold  VPFI_LOW  PFI falling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  VPGB_LOW  PGB low voltage threshold  VPGB_LOW  PGB delay  PGB delay  PGB delay  PGB delay  PGB delay  VIN_OVP pin voltage (VovP) rising  VIN_OVP hysteresis  VIN_OVP hysteresis  VIN_OVP hysteresis  VIN_OVP hysteresis  VIN_OVP hysteresis  VIN_OVP hysteresis  VBUS = 5V, then VIN starts up  PFI is low  VPFI_HIGH  VPFI_HIGH  VPFI_LOW  PFI sink current capability  VPFI_SINK  4mA sink  PGB low voltage threshold  VPGB_LOW  PGB delay  Rising and falling edge		0.81 45	50	V
(OVP) threshold       VIN_OVP       OVP pill Voltage (VOVP) Tisting         VIN_OVP hysteresis       VIN_OVP_HYS       VIN_OVP hysteresis         VSTRG_OVP       VSTRG_OVP       VBUS = 5V, then VIN starts up         VIN to VB isolation MOSFET start-up voltage       IIN_VB_SD       PFI is low         VIN to VB isolation MOSFET shutdown current       IIN_VB_SD       PFI is low         PFI high voltage threshold       VPFI_HIGH         PFI low voltage threshold       VPFI_LOW         PFI falling delay       tPFI_RISING         PFI sink current capability       VPFI_SINK       4mA sink         PGB high voltage threshold       VPGB_HIGH         PGB low voltage threshold       VPGB_LOW         PGB delay       tPGB       Rising and falling edge		45		
VSTRG OVP threshold  VSTRG_OVP  VIN to VB isolation MOSFET start-up voltage  VIN to VB isolation MOSFET shutdown current  PFI high voltage threshold  PFI low voltage threshold  VPFI_HIGH  PFI falling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  VPGB_HIGH  VPGB_LOW  PGB delay  Rising and falling edge				
VIN to VB isolation MOSFET start-up voltage  VIN to VB isolation MOSFET shutdown current  PFI high voltage threshold  PFI low voltage threshold  PFI gelling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  VPGB_LOW  PGB delay  PGB delay  VBUS = 5V, then VIN starts up  PFI is low  PFI LOW  PFI_LOW  PFI_SINK  PFI_RISING  PFI_RISING  PGB_HIGH  VPGB_HIGH  PGB delay  PGB delay  Rising and falling edge		4.4		mV
start-up voltage  VIN to VB isolation MOSFET shutdown current  PFI high voltage threshold  VPFI_HIGH  PFI low voltage threshold  VPFI_LOW  PFI falling delay  PFI rising delay  PFI sink current capability  PFI sink current capability  VPFI_SINK  PGB high voltage threshold  VPGB_HIGH  PGB delay  PGB delay  VBUS = 5V, then VIN starts up  PFI is low  PFI is low  VPFI_HIGH  VPFI_LOW  VPFI_LOW  VPFI_SINK  4mA sink  VPGB_HIGH  VPGB_HIGH  PGB delay  PGB delay  Rising and falling edge		1.1		% of V <sub>FBS</sub> _ REF
shutdown current  PFI high voltage threshold  PFI low voltage threshold  PFI falling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  VPFI_SINK  VPGB_HIGH  PGB delay  PFI si low  VPFI_LOW  VPFI_LOW  VPFI_SING  VPFI_SINK  VPFI_SINK  VPGB_HIGH  VPGB_LOW  PGB delay  Rising and falling edge		0.2		V
PFI low voltage threshold  PFI falling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  PGB low voltage threshold  PGB delay  PGB delay  PFI sink current capability  PGB low falling edge  Rising and falling edge		-250	0	mA
PFI falling delay  PFI rising delay  PFI sink current capability  PGB high voltage threshold  PGB low voltage threshold  PGB delay  PGB delay  Termination  Termi		1.02		% of
PFI rising delay  PFI sink current capability  PGB high voltage threshold  PGB low voltage threshold  PGB delay  PGB delay  Teperature  Te		0.99		V <sub>DET</sub> -
PFI sink current capability  PGB high voltage threshold  PGB low voltage threshold  VPGB_LOW  PGB delay  VPFI_SINK  4mA sink  VPGB_HIGH  VPGB_LOW  Rising and falling edge		0.5		μs
PGB high voltage threshold  PGB low voltage threshold  VPGB_HIGH  VPGB_LOW  PGB delay  temporal tempor		200		μs
PGB low voltage threshold V <sub>PGB_LOW</sub> PGB delay t <sub>PGB</sub> Rising and falling edge			0.3	V
PGB delay t <sub>PGB</sub> Rising and falling edge		0.95		% of
		0.9		V <sub>FBB</sub> _
		5		μs
PGB sink current capability V <sub>PGB_SINK</sub> 4mA sink			0.3	V
PGS high voltage threshold V <sub>PGS_HIGH</sub> PGS threshold bits = 1111		0.97		% of
PGS low voltage threshold V <sub>PGS_LOW</sub> PGS threshold bits = 1111		0.95		V <sub>FBS</sub> _ REF
PGS delay t <sub>PGS</sub> Rising and falling edge		25		μs
PGS sink current capability V <sub>PGS_SINK</sub> 4mA sink			0.3	V
Buck mode valley ILIMIT ILIMIT_VALLEY	5	6.5		Α
Buck release mode switching frequency $f_{SW\_RLS}$ $V_{STRG} = 32V \text{ to } 10V,$ $BUCK\_FSW = 100$	380	480	580	kHz
V <sub>BUS</sub> UVLO rising threshold (10) V <sub>BUS_UVLO_</sub> RISING	2.2	2.35	2.5	V
V <sub>BUS</sub> UVLO hysteresis (10) V <sub>BUS_UVLO_</sub> HYS		0.1		V
Analog-to-Digital Converter (ADC)				
ADC voltage range	0		1.28	V
ADC resolution (12)		10		bits
ADC conversion time (12) ADC conversion for one data bit		45		μs

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# **ELECTRICAL CHARACTERISTICS** (continued)

 $V_{IN}$  = 12V,  $V_{EN}$  = 2V,  $T_J$  = -40°C to 125°C  $^{(9)}$ , typical value is tested at  $T_J$  = 25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Тур	Max	Units	
Logic Interface (SDA, SCL,	Logic Interface (SDA, SCL, INT, SAS, EN)						
High-level input voltage	V <sub>IN_HIGH</sub>	SDA, SCL, SAS, EN	1.2			V	
Low-level input voltage	$V_{\text{IN\_LOW}}$	SDA, SCL, SAS, EN			0.4	V	
Low-level output voltage	Vout_Low	4mA sink, SDA, INT			0.3	V	
Input leakage current	I <sub>IN_LKG</sub>	Connected to 6V, SCL		10		nA	
High level output leakage		Open drain, connected to 6V, SDA		10		nA	
Protection							
Thermal shutdown (12)	$T_{SD}$	Forced backup		150		°C	
Thermal shutdown hysteresis (12)	T <sub>HYS</sub>	Forced backup		25		°C	
Thermal warning (12)	T <sub>WRN</sub>			120		°C	

### Notes:

<sup>9)</sup> Derived from over-temperature (OT) correlation. Not tested in production.

<sup>10)</sup>  $V_{IN}$  UVLO determines the IC's start-up voltage threshold.  $V_{BUS}$  UVLO controls the energy storage and release circuitry. The internal regulator (VCC) is powered by both  $V_{IN}$  and  $V_{BUS}$ . If either  $V_{IN}$  or  $V_{BUS}$  exceeds its respective UVLO threshold, the IC does not shut down.

<sup>11)</sup> See the Start-Up Reset Delay and Bus Voltage Start-Up Slew Rate Control section on page 21 for more details.

<sup>12)</sup> Guaranteed by characterization. Not tested in production.



# I<sup>2</sup>C PORT SIGNAL CHARACTERISTICS

Parameter	Symbol	Condition	Min (13)	Max (13)	Min <sup>(14)</sup>	Max (14)	Units
SCLH and SCL clock frequency	fschl		0	3.4	0	0.4	MHz
Set-up time for a repeated start condition	t <sub>SU_START</sub>		160		600		ns
Hold time for a repeated start condition	thd_start		160		600		ns
SCL clock low period	t <sub>LOW</sub>		160		1300		ns
SCL clock high period	t <sub>HIGH</sub>		60		600		ns
Data set-up time	tsu_data		10		100		ns
Data hold time	thd_data		0	70	0		ns
SCLH signal rise time	trise_sclh		10	40	20 x 0.1C <sub>BUS_LOAD</sub>	300	ns
SCLH signal rise time after a repeated start condition and an acknowledge (ACK) bit	trise_sclh_ RE		10	80	20 x 0.1C <sub>BUS_LOAD</sub>	300	ns
SCLH signal fall time	tfall_sclh		10	40	20 x 0.1C <sub>BUS_LOAD</sub>	300	ns
SDAH signal rise time	trise_sdah		10	80	20 x 0.1C <sub>BUS_LOAD</sub>	300	ns
SDAH signal fall time	tFALL_SDAH		10	80	20 x 0.1C <sub>BUS_LOAD</sub>	300	ns
Set-up time for a stop condition	t <sub>SU;STOP</sub>		160		600		ns
Bus free time between a stop and start condition	tbus_free		160		1300		ns
Data valid time	tvd_data			16		90	ns
Data valid acknowledge time	tvd;ack			160		900	ns
Voltage spike pulse width	tspike	Should be suppressed by the input filter	0	10	0	50	ns
Consoitive load for each		SDAH line, SCLH line		100		400	pF
Capacitive load for each bus line	C <sub>BUS_LOAD</sub>	SDAH line + SDA line, SCLH line + SCL line		400		400	pF

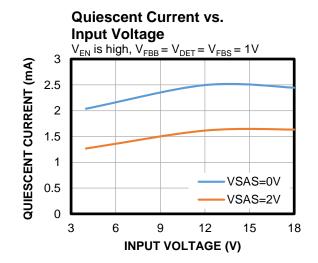
### Notes:

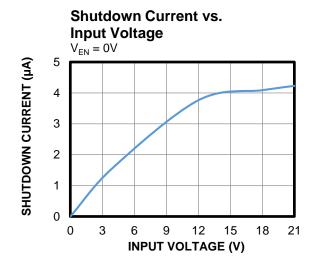
13)  $C_{BUS\_LOAD} = 100pF$ 14)  $C_{BUS\_LOAD} = 400pF$ 

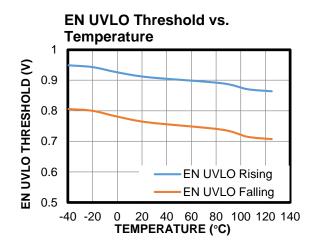


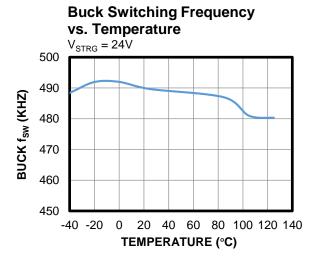
## TYPICAL CHARACTERISTICS

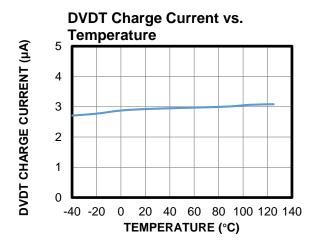
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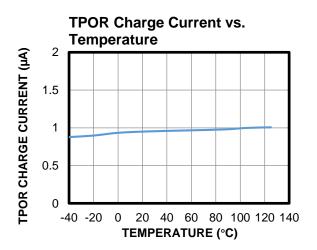








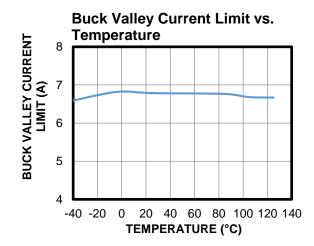


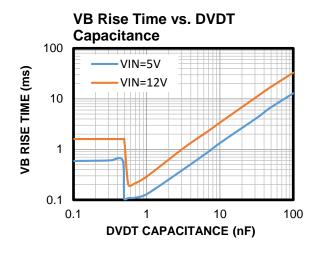


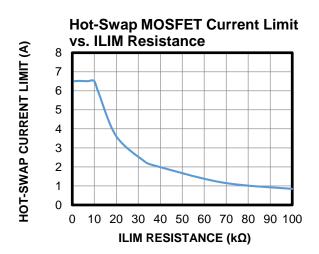


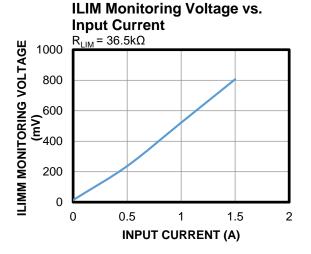
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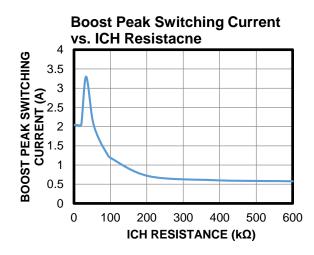
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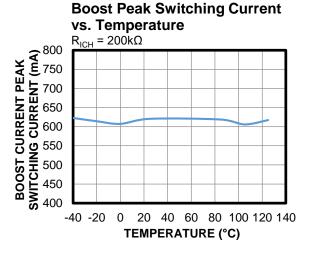








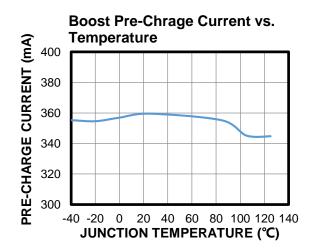


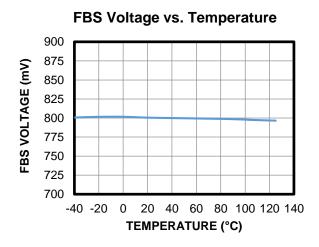


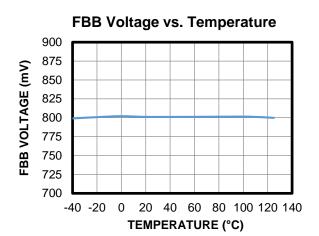


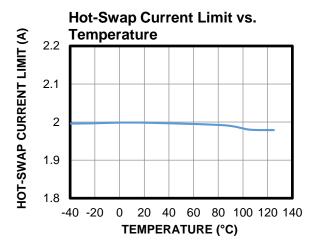
# TYPICAL CHARACTERISTICS (continued)

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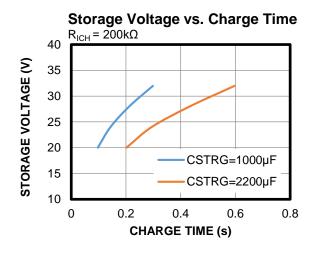


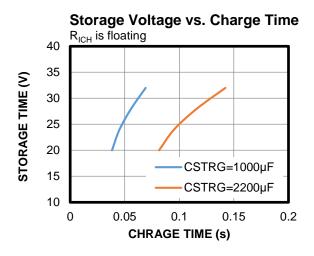


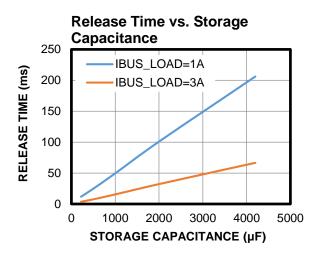


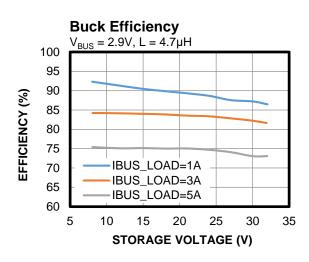
### TYPICAL PERFORMANCE CHARACTERISTICS

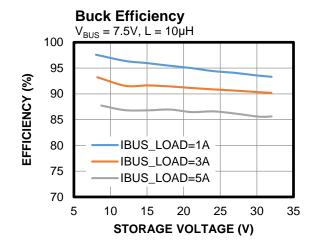
 $V_{IN}$  = 12V,  $V_{STRG}$  = 30V,  $V_{PFI}$  = 8V,  $V_{BUS\_RLS}$  = 7.5V, L = 10 $\mu$ H,  $I_{LOAD}$  = 5A,  $T_A$  = 25°C, unless otherwise noted.

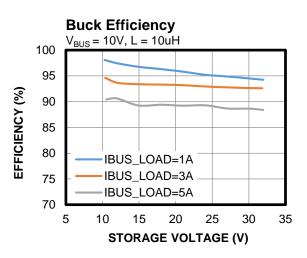








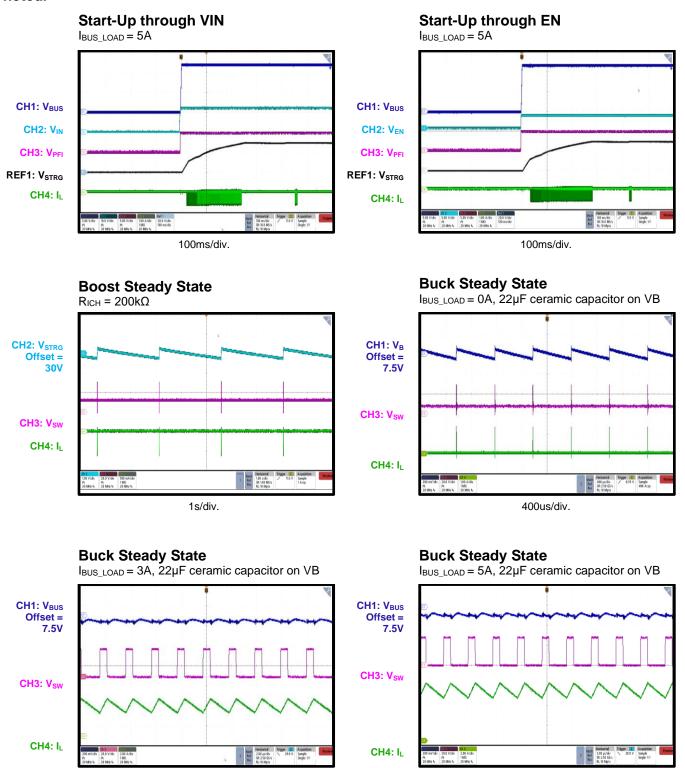






# TYPICAL PERFORMANCE CHARACTERISTICS (continued)

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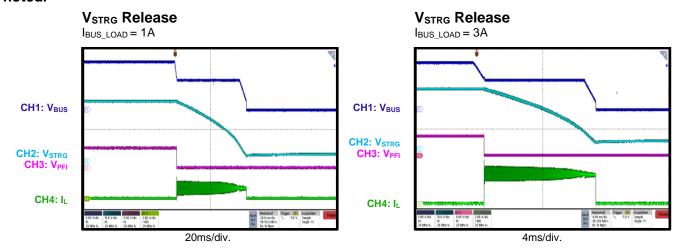
2µs/div.

2µs/div.



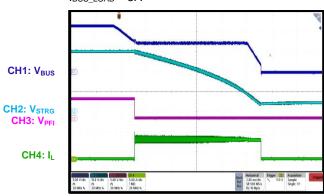
# TYPICAL PERFORMANCE CHARACTERISTICS (continued)

 $V_{IN}$  = 12V,  $V_{STRG}$  = 30V,  $V_{PFI}$  = 8V,  $VB_{RLS}$  = 7.5V, L = 10 $\mu$ H,  $I_{LOAD}$  = 5A,  $T_A$  = 25°C, unless otherwise noted.









2ms/div.



# **FUNCTIONAL BLOCK DIAGRAM**

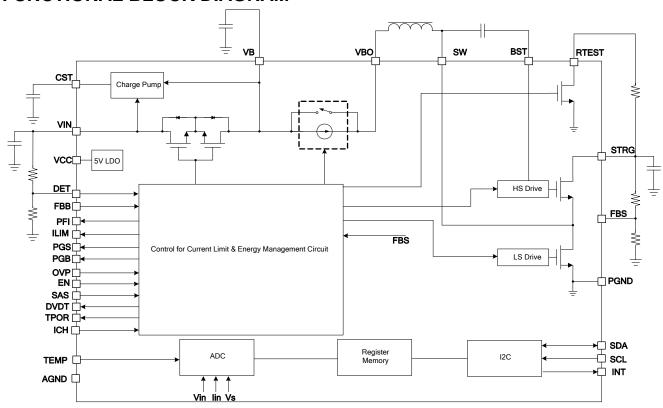


Figure 2: Functional Block Diagram



### **OPERATION**

The MP5514 is an energy storage and management unit in a QFN-30 (5mmx5mm) package. The MP5514 provides a very compact and efficient energy management solution for typical solid-state drives (SSDs) or hard disk drives (HDDs). MPS's patented lossless energy storage and release management circuits use a bidirectional buck-boost converter to achieve optimal energy transfer and provide the most cost-effective energy storage solution.

The integrated boost converter increases the energy storage voltage ( $V_{STRG}$ ) level. The storage feedback resistor divider sets  $V_{STRG}$ . If the input shuts down suddenly, then the internal buck converter transfers the energy from the storage capacitor ( $C_{STRG}$ ) to the bus, and holds the bus voltage ( $V_{BUS}$ ) while the system consumes the energy from  $C_{STRG}$ .

The MP5514 also features an I<sup>2</sup>C interface. The I<sup>2</sup>C interface can be used to write the control command and the monitor system status. An integrated analog-to-digital converter (ADC) converts the voltage, current, and temperature sensor signals.

### Start-Up

If the input voltage ( $V_{IN}$ ) exceeds the undervoltage lockout (UVLO) threshold, then VCC and the I<sup>2</sup>C interface are enabled. If VCC is ready and  $V_{IN}$  exceeds  $V_{BUS}$  by  $\geq 0.2V$  once the poweron reset delay time is complete, then the isolation MOSFET between VIN and VB turns on, and the bus capacitor ( $C_{BUS}$ ) is charged to  $V_{IN}$  according to the DVDT slew rate.

Once the DVDT voltage ( $V_{DVDT}$ ) is saturated, the storage boost converter is unlocked and can be enabled by the register bits. There is a delay time (about 1.2ms) before the boost converter starts up to ensure that the isolation MOSFET is fully on.

The storage boost converter is enabled by default. The  $V_{STRG}$  is charged by a trickle current (about 350mA) during the pre-charge period. Once  $V_{STRG}$  reaches  $V_{BUS}$ , the boost switching circuit is initiated, and  $V_{STRG}$  regulated at the target voltage (see Figure 3).

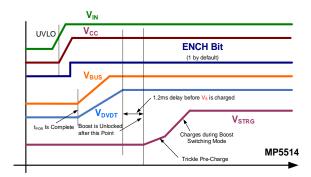


Figure 3: System Power-Up Sequence

### Storage Voltage

After the start-up period, the internal boost converter regulates  $V_{STRG}$  to the set value automatically. The MP5514 uses burst mode to minimize the converter's power loss. If the FBS voltage ( $V_{FBS}$ ) drops below the FBS feedback voltage ( $V_{FBS\_REF}$ ), then the parts enters burst mode and charges  $C_{STRG}$ . Once  $V_{STRG}$  is charged, and  $V_{FBS}$  reaches  $V_{FBS\_REF}$  + FBS\_HYS, the converter stops switching. FBS\_HYS is adjustable via the  $I^2C$ .

During boost charge mode, the boost switching current limit ( $I_{\text{LIMIT}}$ ) and the low-side MOSFET (LS-FET) control the boost converter. If the LS-FET turns on, then the inductor current ( $I_{\text{L}}$ ) increases until it reaches its peak current level (set by ICH). Once  $I_{\text{L}}$  reaches the peak current level, the LS-FET turns off for the set minimum off time. If the feedback voltage is below the internal reference (0.8V) at the end of the minimum off time, then the LS-FET turns on; otherwise, the MP5514 waits until the voltage drops below the reference before the LS-FET turns on again. In boost charge mode, the high-side MOSFET (HS-FET) does not turn on, and  $I_{\text{L}}$  is conducted via the HS-FET body diode.

The boost  $I_{\text{LIMIT}}$  can be configured via the ICH resistor ( $R_{\text{ICH}}$ ). The configured boost switching  $I_{\text{LIMIT}}$  ( $I_{\text{CH}}$ ) can be estimated with Equation (1):

$$I_{CH}(A) = \frac{88}{R_{ICH}(k\Omega)} + \frac{V_{IN}}{L(H) \times 10^7} + 0.1$$
 (1)

Where L is the boost inductor.



The boost switching  $I_{\text{LIMIT}}$  can be configured via  $R_{\text{ICH}}$ . It is recommended to set the boost switching  $I_{\text{LIMIT}}$  between 0.5A and 2A for normal applications. Float ICH to set the boost switching peak current at 2A by default (ICH bits = 11) for typical 12V input and 10 $\mu$ H inductor application conditions. See the ICH register description on page 35 for other boost peak settings while floating ICH.

The MP5514 has  $V_{STRG}$  over-voltage protection (OVP). If the feedback  $V_{STRG}$  on FBS exceeds 1.1 x  $V_{FBS\_REF}$ , then the boost converter's LS-FET turns off until  $V_{STRG}$  drops to the regulation voltage. Additional external power to STRG provided by a voltage exceeding the regulation voltage is not required.

### **Shutdown Release**

Once the first start-up period is complete, and the boost converter starts switching, the MP5514 registers and enables the release function. Once the input power drops and the DET voltage (V<sub>DET</sub>) drops to 0.99 x the V<sub>DET</sub> reference voltage (V<sub>DET\_REF</sub>), then the storage boost converter stops charging and enters buck release mode. At the same time, the isolation MOSFET shuts down to prevent a negative current from flowing between VB and VIN.

In buck release mode, the MP5514 transfers energy from the high-voltage  $C_{\text{STRG}}$  to the low-voltage  $C_{\text{BUS}}$ . The regulated  $V_{\text{BUS}}$  is determined by the  $V_{\text{FBB}}$  reference voltage ( $V_{\text{FBB\_REF}}$ ) and the resistor divider between VB and FBB.

Figure 4 shows the detailed system shutdown process.

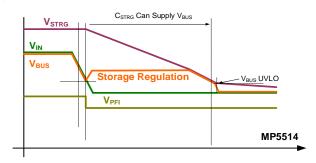


Figure 4: Shutdown through VIN

Buck release mode has a max  $I_{\text{LIMIT}}$  function that limits the release current. In each buck release mode switching cycle, the HS-FET remains off until  $I_{\text{L}}$  drops to the valley  $I_{\text{LIMIT}}$  (typically 6.5A).

### **Input Recovery Start-Up**

If  $V_{\text{IN}}$  fails and is restored, then the MP5514 remains in buck release mode. If  $V_{\text{STRG}}$  is discharged, and  $V_{\text{BUS}}$  drops below the  $V_{\text{BUS}}$  UVLO threshold ( $V_{\text{BUS}\_\text{UVLO}}$ ), then the MP5514 restarts from the recovered  $V_{\text{IN}}$ . This starts a new  $V_{\text{IN}}$  start-up cycle with a start-up reset delay time ( $t_{\text{TPOR}}$ ).

### **Input Current Limit**

The input  $I_{\text{LIMIT}}$  ( $I_{\text{IN\_LIMIT}}$ ) controls the input inrush current of the isolation MOSFET to prevent inrush current from flowing between VIN and VB. The internal DVDT bits or external DVDT capacitor ( $C_{\text{DVDT}}$ ) can set the soft-start time ( $t_{\text{SS}}$ ). In addition to soft start (SS), ILIM can limit the steady-state current by connecting a resistor ( $R_{\text{ILIM}}$ ) between the ILIM and AGND pins to set  $I_{\text{IN\_LIMIT}}$ .  $I_{\text{IN\_LIMIT}}$  can be estimated with Equation (2):

$$I_{IN\_LIMIT} = \frac{70.04}{R_{II.IM}(k\Omega)} + 0.08$$
 (2)

ILIM also monitors and indicates the isolation MOSFET current. The relationship between the input current ( $I_{\text{IN}}$ ) and the ILIM voltage ( $V_{\text{ILIM}}$ ) can be estimated with Equation (3):

$$I_{IN} = \frac{V_{ILIM} \times 64.26}{R_{ILIM}(k\Omega)} + 0.08$$
 (3)

 $V_{\rm ILIM}$  can be read via the ADC.  $V_{\rm ILIM}$  is below 1.09V for normal applications. If a >1.5V voltage is applied to ILIM externally, then the isolation MOSFET shuts down.

If the VB load is close to the ILIM threshold during each boost refresh cycle, then  $I_{\text{IN}}$  may trigger  $I_{\text{IN\_LIMIT}}$ , as well as the system interrupt. To avoid continuously triggering the ILIM interrupt, the input over-current (OC) interrupt is masked automatically during each boost refresh cycle. The mask time depends on the boost switching time.

The OC\_RLS\_EN bit determines the behavior of the backup buck converter once input over-current protection (OCP) is triggered. If OC\_RLS\_EN is set to 1, then the backup buck converters starts up to maintain  $V_{\text{BUS}}$  once input OCP is triggered and the FBB voltage ( $V_{\text{FBB}}$ ) drops to  $V_{\text{FBB},\text{REF}}$ . Once  $V_{\text{FBB}}$  is charged to



105% of  $V_{\text{FBB\_REF}}$ , the buck converter turns off. The buck converter is off during the boost refresh cycle, even if OCP is triggered. If OC\_RLS\_EN is set to 0, then the backup buck converter cannot be turned on by FBB.

The isolation MOSFET also has fast OCP for extreme OC conditions. This is the second level of OCP. The fast OCP threshold is about 11A, with a ±10% tolerance. Once fast OCP is triggered, the isolation MOSFET turns off without entering buck release mode. The MOSFET turns on again once the OC fault is removed and VIN is present.

### Start-Up Reset Delay and Bus Voltage Start-Up Slew Rate Control

TPOR controls the power-on reset function for hot swapping. Float TPOR to set the start-up reset delay time ( $t_{TPOR}$ ) to its default time (about 1.5ms). If an external capacitor is connected to TPOR, then an internal 1µA current charges the capacitor between 0V and 1V, and determines  $t_{TPOR}$ .  $t_{TPOR}$  can be estimated with Equation (4):

$$t_{TPOR} = \frac{C_{TPOR} \times 1V}{1\mu A}$$
 (4)

After  $t_{TPOR}$ , a capacitor across DVDT sets the VB  $t_{SS}$ . During  $t_{SS}$ , the relationship between VB and DVDT can be estimated with Equation (5):

$$VB = 13 \times V_{DVDT}$$
 (5)

Where  $V_{DVDT}$  is the DVDT capacitor voltage charged by a  $3\mu A$  current.

The V<sub>DVDT</sub> charge is saturated to about 1.23V.

 $t_{SS}$  between 0V and  $V_{IN}$  can be estimated with Equation (6):

$$t_{SS} = \frac{VB \times C_{DVDT}}{13 \times 3\mu A}$$
 (6)

Float DVDT to configure the VB rise time via the internal DVDT register bits. By default, the DVDT bit is set to 00, and the VB slew rate is about 7.5V/ms. If DVDT is floating, the VB rise time from 0V to 12V is 1.6ms by default.

### **Reverse-Current Protection (RCP)**

The VIN to VB MOSFET turns on once  $V_{IN}$  exceeds its UVLO rising threshold ( $V_{IN\_UVLO\_RISING}$ ) and ( $V_{BUS}$  + 0.2V). This MOSFET turns off once  $V_{DET}$  drops, and the MP5514 enters buck release mode. The MOSFET does

not turn on again until the part exits buck release mode.

If energy from the storage capacitors is released to VB, then the isolation MOSFET circuit employs reverse-current protection (RCP). A 250mA reverse current from VB to VIN typically shuts down the isolation MOSFET.

### **Start-Up Sequence**

After start-up, the MP5514 operates with the  $t_{TPOR}$  and DVDT  $t_{SS}$ . During the VB rise time, an internal charge pump charges the CST capacitor ( $C_{CST}$ ). This provides a driver source for the hotswap MOSFET. A shorter DVDT time may trigger the input current-limit threshold. A larger  $C_{CST}$  may affect the charge-pump slew rate. It is recommended that  $C_{CST}$  be 10nF. During the DVDT  $t_{SS}$ , the VB capacitor ( $t_{CVB}$ ) is charged, and  $t_{CSTRG}$  is not charged.

Once  $C_{VB}$  is charged,  $V_{DVDT}$  charges to about 1.23V and is held at the saturated voltage. If PFI is high and DVDT is saturated, then the charge function is enabled and  $C_{STRG}$  charges to the target voltage.

### **Storage Capacitor Test**

The MP5514 provides a capacitor test function that discharges  $C_{\text{STRG}}$  via an external resistor connected between STRG and RTEST. Figure 5 shows the  $C_{\text{STRG}}$  test circuit.

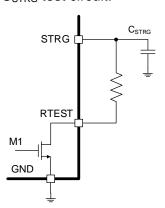


Figure 5: Storage Capacitor Test Circuit

The MOSFET is about  $4.5\Omega$ , and the peak discharge current should be limited to below 500mA via an external resistor (even if it is discharged in a short time).

If the START\_CAP\_TEST bit is set, then the MP5514 disables boost charge switching, and

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RTEST is connected to GND via the internal MOSFET (M1) for energy discharging. The MP5514 enables V<sub>STRG</sub> ADC conversion once V<sub>FBS</sub> drops below the V<sub>FBS</sub> REF threshold. The system-on-chip (SoC) can read V<sub>STRG</sub> via the I<sup>2</sup>C. Simultaneously, an internal counter is enabled to measure the discharge time. The counter continues until the capacitor voltage drops below the PGS threshold. Once V<sub>STRG</sub> drops to the PGS threshold, the ADC reads V<sub>STRG</sub> again, and the CAP TEST DONE bit is set to indicate that the capacitor test is complete. CAP\_TEST\_DONE produces one interrupt signal to inform the SoC that the test has been completed. The SoC can read V<sub>STRG</sub> and the counter timer register. With the initial voltage and end voltage reading, the SoC determines whether the discharge time is acceptable.

At the first ADC conversion, the MP5514 reads VSTRG and stores it the ADC\_BACKUP\_VOLTAGE\_DATA2 register. Once the capacitor is discharged, the ADC records the end voltage the to ADC\_BACKUP\_VOLTAGE\_DATA1 register. counter result is stored the CAP TEST TIMER register.

Once the capacitor test is complete, the START\_CAP\_TEST bit is reset, and the recharge function is enabled. Figure 6 on page 23 shows the capacitor test flowchart.

The SoC capacitor test function operates as follows:

- Write "1" to register 04h, bit[2] and bit[6] to mask the PGS not good interrupt and ADC complete input.
- 2. Write a value to register 06h, bits[3:0] to set the PGS threshold. Write "00" to register 06h, bits[3:0] to set the PGS threshold at 80% of  $V_{\rm STRG}$ .
- 3. If  $V_{\text{IN}}$  is below 3.8V, then write "1" to register 1Bh, bit[1] to turn on the internal  $V_{\text{STRG}}$  for the VCC LDO. If  $V_{\text{IN}}$  exceeds 3.8V, then ignore this step.
- 4. Write "1" to register 01h, bit[3] to start the capacitor test. The MP5514 disables the V<sub>STRG</sub> charge function once V<sub>STRG</sub> exceeds the set V<sub>FBS</sub>. Register 01h, bit[0] does not change. Once V<sub>STRG</sub> is charged, C<sub>STRG</sub> is discharged via an external resistor. The ADC

- starts once  $V_{FBS}$  drops below the  $V_{FBS\_REF}$  threshold. The ADC reads  $V_{STRG}$ , and stores data in ADC\_BACKUP\_VOLTAGE\_DATA2 register. The internal timer starts once  $V_{FBS}$  drops below the  $V_{FBS\_REF}$  threshold.
- 5. If register 02h, bit[7] is set to 1, then the capacitor test is complete once the interrupt signal is received from the MP5514. Once V<sub>STRG</sub> drops to the PGS threshold, the part stops discharging V<sub>STRG</sub>, and the timer value is written to the CAP\_TEST\_TIMER register. If the PGS falling threshold is triggered, then the MP5514 starts up the ADC again and stores the data in the ADC\_BACKUP\_VOLTAGE\_DATA1 register. Once ADC conversion is complete, the MP5514 sets the CAP\_TEST\_DONE bit. Register 01h, bit[3] is reset to 0 to clear the START\_CAP\_TEST bit. The boost charge function is enabled automatically.
- 6. Read register 12h, bits[7:0] and register 13h, bits[1:0] to store the final voltage (V<sub>FINAL</sub>) (10 bits total). Register 12h is the high byte, and register 13h is the low byte. Read register 14h, bits[7:0] and register 15h, bits[1:0] to the initial voltage (V<sub>INITIAL</sub>) (10 bits total). Register 14h is the high byte, and register 15h is the low byte. Read register 16h, bits[7:0] and register 17h, bits[7:0] to store the time (16 bits total). Register 16h is the low byte, and register 17h is the high byte.
- 7. Write "1" to register 02h, bit[7] to reset the capacitor test interrupt. Write "1" to register 04h, bit[2] and bit[6] to enable the PGS\_NOT\_ OK and ADC\_DONE functions. If register 1Bh, bit[1] was set to 1 in step 3, write "0" to this bit.
- 8. The ADC results can be calculated with Equation (7):

$$C_{STRG} = \frac{Time}{R_{DISCH} \times In(\frac{V_{INITIAL} + R_{DISCH} \times I_{LDO}}{V_{FINAL} + R_{DISCH} \times I_{LDO}})}$$
(7)

Where  $V_{\text{INITIAL}}$  is  $V_{\text{STRG}}$  before the discharge timer starts (stored in ADC\_BACKUP\_VOLTAGE\_DATA2),  $V_{\text{FINAL}}$  is  $V_{\text{STRG}}$  after being discharged (stored in ADC\_BACKUP\_VOLTAGE\_DATA1),  $R_{\text{DISCH}}$  is the resistor between STRG and RTEST, and  $I_{\text{LDO}}$  is the VCC LDO current.



If V<sub>IN</sub> drops below 5V, and register 1Bh, bit[1] is set to 1, then I<sub>LDO</sub> is typically 2mA; otherwise, I<sub>LDO</sub> is 0mA. Once the capacitor test is complete, reset the LDO EN bit to save the operation current (the LDO unit for the capacitor test should be mA). The time is recorded in the CAP\_TEST\_TIMER register (the unit for the register data is 1ms).

See the ADC Results section on page 37 for the test times and voltage calculations.

If V<sub>IN</sub> fails during the capacitor test, then the MP5514 enters buck release mode. The capacitor test does not work in buck release mode. In buck release mode, the capacitor test cannot start, and "1" cannot be written to START CAP TEST.

If an OC fault occurs during the capacitor test, and OC RLS EN is set to 1, then the capacitor test stops. The isolation MOSFET clamps the current, and the backup circuit enters buck release mode to support the additional current.

For more information, refer to the MPS application note AN125.

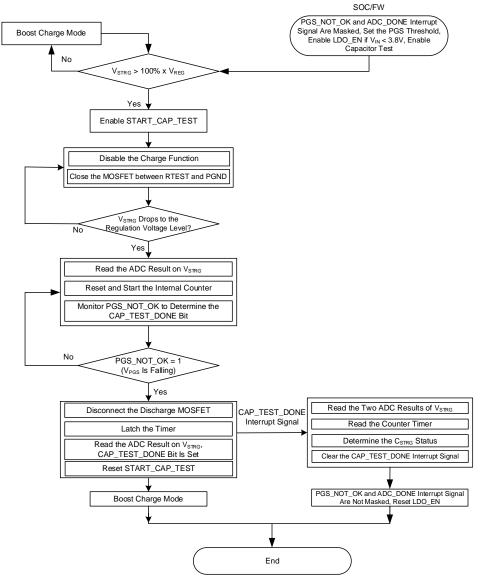


Figure 6: Storage Capacitor Test Flowchart



### **VCC Power Management**

The MP5514's internal circuitry is powered by the VCC capacitor ( $C_{VCC}$ ). VCC is supplied by  $V_{IN}$ ,  $V_{BUS}$ , or  $V_{STRG}$  (see Table 1).

**Table 1: VCC Power Sources** 

Operation Mode	LDO_EN Bit	Power Source
Boost charge	0 (default)	VCC is supplied by V <sub>IN</sub> or V <sub>BUS</sub> (whichever is higher)
Buck discharge	0 (default)	If Vcc > 4.5V, then VCC is supplied by V <sub>IN</sub> or V <sub>BUS</sub>
Boost charge	1	(whichever is higher). If Vcc < 4.5V, then the LDO
Buck discharge	1	between STRG and VCC is enabled and regulates Vcc at about 4.5V.

The LDO\_EN bit (register 1Bh, bit[1]) is used for ADC conversion, including the capacitor test while  $V_{\text{IN}}$  and  $V_{\text{BUS}}$  are low. If  $V_{\text{IN}}$  and  $V_{\text{BUS}}$  are low, enable the LDO\_EN bit before ADC operation. See to the 10-Bit Analog-to-Digital Converter (ADC) section on page 25 for more details.

A ≥1μF capacitor is required on VCC. If the part starts up from a ≤3V  $V_{IN}$ , then  $V_{CC}$  is low due to the VIN to VCC voltage drop. Any external current on VCC (e.g. a PFI pull-up resistor) pulls  $V_{CC}$  down, and makes it difficult to start up the MP5514. It is recommended to use a 100k $\Omega$  pull-up resistor for the PFI and INT pins. If  $V_{BUS}$  is below 5V, then PFI and INT can be pulled up to  $V_{BUS}$ .

The MP5514 can start up from a low  $V_{\text{IN}}$  (2.7V) at ≥25°C temperatures. If the temperature is below 25°C, then the UVLO threshold increases. Connect an external Schottky diode between the VIN and VCC pins to have the IC start up from a 2.7V  $V_{\text{IN}}$  at low temperatures (below 25°C). It is recommended to add this diode, even if  $V_{\text{IN}}$  is 3V at temperatures below -40°C.

### **Enable (EN) Control**

The MP5514's enable (EN) pin works with the EN bit to enable the internal circuit. The MP5514 is enabled once both the EN pin and EN bit are high. During application, the EN pin cannot be connected to a voltage exceeding 6.5V. For resistor pull-up conditions, an internal Zener diode clamps the voltage at the EN pin voltage ( $V_{EN}$ ). The maximum pull-up current for the internal Zener diode should be <1mA. 100k $\Omega$ 

pull-up resistors connected to both VIN and VB are recommended if the resistors are pulled up to  $V_{\text{IN}}$  and  $V_{\text{BUS}}$ .

### **SAS Function**

The MP5514 provides a forced backup mode for energy discharging. This function works together with the SAS\_DLY, SAS\_ASSERT\_TIME, and SAS\_NEGATE\_TIME I<sup>2</sup>C register bits.

After start up, the MP5514 ignores the SAS voltage (V<sub>SAS</sub>) being pulled high for the time set via the SAS DLY bit. If V<sub>SAS</sub> remains high for time than the set via SAS\_ASSERT\_TIME bit, then the isolation MOSFET turns off, the part enters buck release mode, and the PFI voltage (VPFI) is pulled low to indicate the power status. If V<sub>BUS</sub> drops below V<sub>BUS UVLO</sub> before SAS negates, then the buck converter shuts down, and V<sub>CC</sub> continues working. The MP5514 operates with a new start cycle once SAS is negated by holding V<sub>SAS</sub> low for the time set via the SAS\_NEGATE\_TIME bit. If V<sub>BUS</sub> exceeds V<sub>BUS</sub> <sub>UVLO</sub> while SAS is negated. then V<sub>PFI</sub> is pulled high, and the isolation MOSFET operates as the V<sub>IN</sub> power recovery once V<sub>BUS</sub> triggers V<sub>BUS</sub> UVLO.

### **Input Power Failure Indicator (PFI)**

If  $V_{DET}$  drops below 0.99 x  $V_{DET\_REF}$ , then  $V_{PFI}$  is pulled low internally to indicate a power failure, and the part exits boost charge mode. If  $V_{DET}$  exceeds 1.02 x  $V_{DET\_REF}$ , then  $V_{PFI}$  is pulled high (if it is pulled up via an external resistor). The MP5514 does not exit buck release mode until  $V_{BUS}$  is discharged to  $V_{BUS\_UVLO}$  or the IC resets (even if  $V_{PFI}$  is high).

### **Bus Voltage Power Good (PG) Indication**

If the bus feedback voltage ( $V_{FBB}$ ) drops below 0.9 x  $V_{FBB\_REF}$ , then PGB is pulled low internally. If  $V_{FBB}$  exceeds 0.95 x  $V_{FBB\_REF}$ , then PGB is pulled high.

### Storage Voltage PG Indication

The storage power good (PG) threshold can be configured via by the PGS threshold bits (register 06h, bits[3:0]). The default PGS falling threshold is 95% of V<sub>FBS\_REF</sub>. If the storage feedback voltage (V<sub>FBS</sub>) drops below 0.95 x V<sub>FBS\_REF</sub>, then PGS is pulled low internally. If V<sub>FBS</sub> exceeds 0.97 x V<sub>FBS\_REF</sub>, then PGS is pulled high.



## **Input Over-Voltage Protection (OVP)**

A resistor divider from  $V_{IN}$  to OVP sets the input over-voltage protection (OVP) threshold ( $V_{IN\_OVP}$ ). Once the OVP pin voltage ( $V_{OVP}$ ) exceeds 0.81V, the MP5514 enters buck backup mode. Once  $V_{OVP}$  drops below 0.765V, and the buck stop operating,  $V_{BUS}$  triggers  $V_{BUS\_UVLO}$ , and the MP5514 restarts automatically via a new start-up cycle with a TPOR process. An INPUT\_OVER-VOLTAGE register bit records the OVP event, and generates an interrupt signal on INT if it is unmasked.

### 10-Bit Analog-to-Digital Converter (ADC)

The MP5514 integrates a 10-bit ADC to measure  $V_{IN}$ ,  $I_{IN}$ ,  $V_{STRG}$ , and the TEMP pin's temperature sensor voltage. The START\_ADC register enables ADC conversion. ADC\_DONE bit is set if an ADC conversion completes. An interrupt request to the controller can be set if the ADC\_DONE bit is set. Figure 7 shows the ADC setting flowchart. See the ADC Results register on page 37 for more details.

If V<sub>IN</sub> drops below 3.8V, use the host chip to set register 0x1Bh, bit[1] to 1 before enabling the ADC or capacitor test functions. Setting this bit enables the LDO between STRG and VCC, provides more margins for the internal ADC reference, and insures ADC accuracy. The LDO draws about 2mA of current from STRG. The LDO should be disabled once ADC conversion or the capacitor test is complete. The LDO\_EN bit is set to 0 by default.

### **Interrupt Control**

If a fault condition in the interrupt register occurs when the fault bits are not masked, then the INT pin is pulled high. This interrupt signal is asserted to indicate to the SoC that a fault has occurred. While there is an existing interrupt event, and a second interrupt event can occur before the SoC resets INT (while the INT voltage is high). The MP5514 keeps INT high until the SoC resets all interrupt events (see Figure 8).

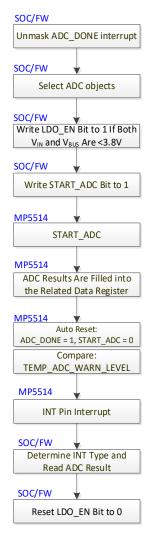


Figure 7: ADC Converter Flowchart

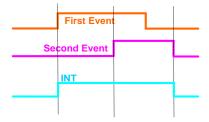


Figure 8: Interrupt Sequence

If a fault occurs, the MP5514 generates an interrupt and other actions (see Table 2 on page 26).



### I<sup>2</sup>C Timeout

If SCL is pulled low or high for up to 25ms, or SDA is pulled low for up to 450ms, the I<sup>2</sup>C is reset. The I2C timeout function can be enabled by setting I2C TO EN to 1, and can be disabled by setting I2C\_TO\_EN to 0.

### **Thermal Shutdown**

Thermal shutdown prevents the chip from operating at exceedingly high temperatures. If the junction temperature (T<sub>J</sub>) exceeds 120°C, the IC TJ WARN bit is set to 1, which sends an interrupt signal to the SoC. Write 1 to the IC TJ WARN bit to reset the interrupt event once the temperature drops below 100°C.

If T<sub>J</sub> exceeds 150°C, the MP5514 enters buck backup mode, and discharges energy from V<sub>STRG</sub> to V<sub>BUS</sub>. In this scenario, the isolation MOSFET

is off and PFI is low. The buck is released until the energy is fully discharged. Once T<sub>J</sub> drops below 125°C, the MP5514 starts up again through VIN, and operates as the V<sub>IN</sub> power recovery. There is an interrupt signal for a 150°C over-temperature (OT) fault. This interrupt signal can be reset by writing 1 to the IC TJ WARN bit.

If T<sub>J</sub> exceeds 165°C, the device shuts down.

### Register Default Value Configuration

The MP5514 has multiple control register bits, all of which have a fixed default value after a power reset. After start-up, all of the bits can be configured by writing to the I2C. Registers 0x06h, 0x07h, 0x21h, 0x26h, and the device I2C address default value can be configured. Different default values can be configured to fit different system requirements.

**Table 2: Fault Response** 

Event	Status Bit	Status/INT Reset Condition	PFI	INT	MP5514 Power Action
Input OC fault	INPUT_OVER- CURRENT	POR, write 1 to this bit	No action	Yes (high)	The device limits I <sub>IN</sub> ; If OC_RLS_EN = 1, then the buck starts up once V <sub>BUS</sub> drops below V <sub>FBB_REF</sub>
Input power failure	N/A	N/A	Yes (low)	No action	The isolation MOSFET is off, and the IC enters buck release mode
OVP pin over-voltage (OV) fault	INPUT OVER- VOLTAGE	POR, write 1 to this bit	Yes (low)	Yes (high)	The isolation MOSFET is off, and IC enters buck release mode
V <sub>STRG</sub> triggers PGS falling threshold	PGS_NOT_OK	POR, write 1 to this bit	No action	Yes (high)	No action
TEMP pin warning	TEMP_WARN	POR, write 1 to this bit	No action	Yes (high)	No action
Die high-temperature warning	IC_TJ_WARN	POR, write 1 to this bit	No action	Yes (high)	No action
Die OT to forced buck	IC_TJ_ SHUTDOWN	POR, write 1 to this bit	Yes (low)	Yes (high)	The isolation MOSFET is off, and the IC enters buck release mode, then shuts down once the power is discharged
SAS disabled supply	SAS_DIS	POR, write 1 to this bit	Yes (low)	Yes (high)	The isolation MOSFET is off, and the IC enters buck release mode
ADC complete	ADC_DONE	POR, write 1 to this bit	No action	Yes (high)	No action
Capacitor test complete	CAP_TEST_ DONE	POR, write 1 to this bit	No action	Yes (high)	See Figure 6 on page 23



It is suggested to use the default register value of registers 0x06h, 0x07h, 0x21h, and device I<sup>2</sup>C address for application. If different default values are needed for these registers, please contact MPS for a program solution.

### I<sup>2</sup>C Interface

The I<sup>2</sup>C is a two-wire, bidirectional, serial interface consisting of a data line (SDA) and a clock line (SCL). The lines are pulled to a bus voltage externally when they are idle. When connecting to the line, a master device generates the SCL signal and device address and arranges the communication sequence. The MP5514 interface is an I<sup>2</sup>C slave. The I<sup>2</sup>C interface adds flexibility to the SSD power system control by different register configurations.

The MP5514 7-bit device address is defined as 33h (011 0011). When the master sends an 8-bit address value, the 7-bit I<sup>2</sup>C address should be followed by a 0 or 1 to indicate a write or read operation, respectively.

### I<sup>2</sup>C Data Validity

One clock pulse is generated for each data bit transferred. The data on the SDA line must be stable during the high period of the clock. A high or low state of the data line can change only when the clock signal on the SCL line is low as shown in Figure 9.

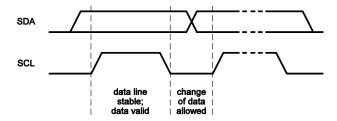


Figure 9: Bit Transfer on the I<sup>2</sup>C Bus

The start and stop are signaled by the master device, which signifies the beginning and the end of the I<sup>2</sup>C transfer. The start condition is defined as the SDA signal transitioning from high to low while the SCL is high. The stop condition is defined as the SDA signal transitioning from low to high while the SCL is high (see Figure 10).

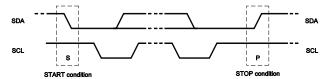


Figure 10: Start and Stop Conditions

Start and stop conditions are always generated by the master. The bus is considered to be busy after the start condition. The bus is considered to be free again after a minimum of 4.7µs after the stop condition. The bus stays busy if a repeated start (Sr) is generated instead of a stop condition. The start (S) and repeated start (Sr) conditions are identical functionally.

### I<sup>2</sup>C Transfer Data

Every byte put on the SDA line must be eight bits long. Each byte must be followed by an acknowledge bit. The acknowledge-related clock pulse is generated by the master. The transmitter releases the SDA line (high) during the acknowledge clock pulse. The receiver must pull down the SDA line during the acknowledge clock pulse so it remains stable low during the high period of this clock pulse.

Data transfers follow the format shown in Figure 11. After the start condition (S), a slave address is sent. This address is seven bits long followed by an eighth bit, which is a data direction bit (R/W). A zero (0) indicates a transmission (write), and a one (1) indicates a request for data (read). A data transfer is always terminated by a stop condition (P) generated by the master. However, if a master still wishes to communicate on the bus, it can generate a repeated start condition (Sr) and address another slave without first generating a stop condition.

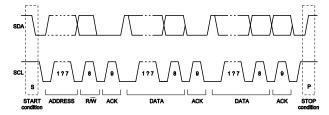


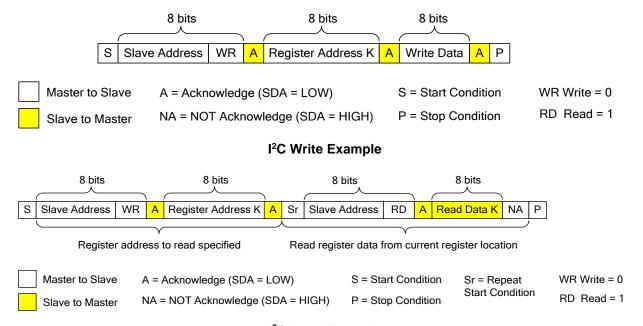
Figure 11: Complete Data Transfer



The MP5514 includes a full I<sup>2</sup>C slave controller. The I<sup>2</sup>C slave fully complies with the I<sup>2</sup>C specification requirements and requires a start condition, a valid I<sup>2</sup>C address, a register address byte, and a data byte for a single data update. After receiving each byte, the MP5514 acknowledges by pulling the SDA line low during

the high period of a single clock pulse. A valid I<sup>2</sup>C address selects the MP5514. The MP5514 performs an update on the falling edge of the LSB byte.

Figure 12 shows an example of an I<sup>2</sup>C read and write command.



I<sup>2</sup>C Read Example

Figure 12: I<sup>2</sup>C Read and Write



# **ONE-TIME PROGRAMMABLE MEMORY (OTP)**

### **Table 3: OTP Table**

Address	Name	D[7]	D[6]	D[5]	D[4]	D[3]	D[2]	D[1]	D[0]
0x06h	BACKUP_CAP_ THRESHOLD	FBS_HYS	VIN_ RECOVER_ MODE	IC	СН	PGS_THRESHOLD			
0x07h	TEMP_WARN_ THRESHOLD	EFUSE_U	EFUSE_UVLO OC_RLS_ EN			TEMP_ADC_WARN_LEVEL			
0x08h	REVERSE_ CURRENT_ FAST_OFF	REVERSE_ CURRENT_FAST _OFF_DISABLE	-	ı	-	-	-	ı	ı
0x21h	SYS_CONTROL_3	INTERNAL_ILIM_THRESHOLD			DV	DT	TP	OR	EN
0x26h	SAS_CONTROL	I2C_TO_EN	SAS_DLY	SAS_ASS	ERT_TIME	SAS_NEG	ATE_TIME	ı	-

### **Table 3: Default OTP Values**

Register	D[7]	D[6]	D[5]	D[4]	D[3]	D[2]	D[1]	D[0]
06h	FBS_HYS (0: 9mV)	VIN_RECOVER_ MODE (0: Operates in buck release mode until V <sub>BUS</sub> drops below V <sub>BUS_UVLO</sub> once V <sub>IN</sub> recovers)	ICH (11: 2A	)	PGS_THRESHOLD (1111: 95% o			5% of V <sub>FBS_REF</sub> )
07h	EFUSE_UVLO (1 3.4 falli	OC_RLS_EN (0: PLP enter buck release mode only if DET is triggered)		TEMP_ADC_WARN_LEVEL (11111)				
08H	RC_FAST_OFF_ DISABLE (0: Enabled)	-	-	ı	-	-	-	-
21h	INTERNAL_ILIM_THRESHOLD ((		100·66A) I		DVDT TPOF 7.5V/ms) (00: 1.6r		-	EN (1: Enabled)
26h	I2C_TO_EN (1: I <sup>2</sup> C resets if SCL is pulled low or high for up to 25ms, or if SDA is pulled low for up to 450ms)	SAS_DLY (1: 30s)	SAS_ASSERT_ (10: 5s)	TIME		ATE_TIME 30s)	-	-



# I<sup>2</sup>C REGISTER MAP

Addres s	Register	Туре	D[7]	D[6]	D[5]	D[4]	D[3]	D[2]	D[1]	D[0]	Reset State	
00h	VENDOR_ID	R	F.	AΒ	MAJO	R_REV	MINO	R_REV	VENI	DOR_ID	0000 0000	j
01h	SYSTEM_ CONTROL_1	R/W	-	-	-	-	START_CAP_ TEST	START_ADC	-	ENCH	0000 0001	
02h	INTERRUPT1 STATUS	R/W	CAP_TEST _DONE	ADC_DON E	-	INPUT_OVE R- CURRENT	INPUT_OVER -VOLTAGE	PGS_ NOT_OK	-	TEMP_WAR N	0000 0100	
03h	INTERRUPT2 STATUS	R/W	-	SAS_DIS	ISOFET_O FF	IC_TJ_ SHUTDOWN	IC_TJ_WARN	-	-	-	0010 0000	
04h	INTERRUPT1 _MASK_ CONTROL	R/W	CAP_TEST _DONE_ MASK	ADC_DON E_MASK	-	INPUT_OVE R- CURRENT_ MASK	INPUT_OVER -VOLTAGE_ MASK	PGS_ NOT_OK_MAS K	-	TEMP_WAR N_MASK	0010 0100	
05h	INTERRUPT2 _MASK_ CONTROL	R/W	-	SAS_DIS_ MASK	ISOFET_ OFF_MAS K	IC_TJ_ SHUTDOWN _MASK	IC_TJ_WARN _MASK	-	-	-	0010 0101	
06h	BACKUP_CA P_THRESHO LD	R/W	FBS_HYS	VIN_ RECOVER _MODE	IC	СН		PGS_THRES	SHOLD		0011 1111	
07h	TEMP_WARN _THRESHOL D	R/W		_UVLO	OC_RLS_E N		TEMP_	ADC_WARN_LE	VEL		1101 1111	
08h	REVERSE_ CURRENT_ FAST_OFF	R/W	REVERSE_ CURRENT FAST_OFF DISABLE	-	-	-	-	-	-	-	0001 1110	
09h	ADC_SOURC E _SELECT	R/W	-	-	-	BACKUP_ VOLTAGE	-	TEMP_ PIN	INPUT_ CURREN T	INPUT_ VOLTAGE	0000 0000	
0Ah	ADC_INPUT_	R		•		VIN_F	IIGH_BYTE	•	•		0000 0000	
0Bh	VOLTAGE_ DATA	R	-	-	-	-	-	-	VIN_LC	DW_BYTE	0000 0000	
0Ch	ADC_INPUT_	R				I_IN_F	HIGH_BYTE				0000 0000	1
0Dh	CURRENT_ DATA	R	-	-	-	-	-	-	I_IN_LC	OW_BYTE	0000 0000	
0Eh	ADC_TEMP_	R		ı	ı	TEMP_	HIGH_BYTE	1			0000 0000	1
0Fh	VOLTAGE_ DATA	R	-	-	-	-	-	-	TEMP_L	OW_BYTE	0000 0000	
12h	ADC_BACKU	R				VSTRG1	_HIGH_BYTE				0000 0000	1
13h	P_ VOLTAGE_ DATA1	R	-	-	-	-	-	-	VSTRG1_	LOW_BYTE	0000 0000	
14h	ADC_BACKU	R		U		VSTRG2	HIGH_BYTE	•			0000 0000	j
15h	P_VOLTAGE DATA2	R	-	-	-	-	-	-	VSTRG2_	LOW_BYTE	0000 0000	
16h	CAP_TEST_	R				CAP_TEST_T	IMER_LOW_B	YTE			0000 0000	1
17h	TIMER	R				CAP_TEST_T	IMER_HIGH_B	YTE		1	0000 0000	
1Bh	VIN_RECOVE R_CONTROL	R/W	-	-	-	-	-	-	LDO_EN	-	0000 0000	
1Fh	RESERVED	R	-				RESERVED (	13)			0011 0011	L
20h	SYS_ CONTROL_2	R/W	RESERVE D (13)	INPUT_ILI MT SET	RESERVE D (13)	RESERVED		BUCK_FS	SW		FORCE_BU CK_RELEAS E	
21h	SYS_ CONTROL_3	R/W	INTERNA	L_ILIM_THR	RESHOLD		DVDT		T	POR	EN	
22h	SYS_ CONTROL_4	R/W	-	-	-		=	ILIM_EN		ILIM_TUNE	<u> </u>	
26h	SAS_ CONTROL	R	I2C_TO_E N	SAS_DLY	SA	S_ASSERT_	TIME	SAS_NEGAT	E_TIME	RESERVED	RESERVED	

### Note:

15) Reserved bits. Do not write different values to these bits in application.



# Vendor ID (00h)

Access: Read-only

Bits	Name	Description	Default Value
7:6	FAB	Fab location.	00
5:4	MAJOR_REV	Major revision.	00
3:2	MINOR_REV	Minor revision.	00
1:0	VENDOR_ID	Vendor ID.	00

# System Control 1 (01h)

Bits	Name	Description	Default Value
D[3]	START_CAP_	Capacitor test start enable bit. If the input voltage (V <sub>IN</sub> ) is below 3.8V, then the LDO_EN bit should be set to 1 before the capacitor test starts. The LDO_EN bit should be disabled once the capacitor test is complete.	00
	TEST	Starts the capacitor test on the storage capacitors; resets to 0 once the capacitor test is complete     Capacitor test function is disabled	
Diai	START_ADC	Analog-to-digital converter (ADC) conversion enable bit. The LDO_EN bit should be set to 1 before starting the ADC. If both $V_{\text{IN}}$ and VB are below 3.8V, then disable the LDO_EN bit after ADC is completed.	00
D[2]		ADC conversion begins; resets to 0 once the capacitor test is complete     An ADC conversion event has not occurred	00
D[0]	ENCH	Storage boost enable bit. This bit cannot be written to in buck release mode. This bit does not affect buck release mode once the storage voltage ( $V_{STRG}$ ) is charged high (even if ENCH is set to 0).	00
		Boost charge function is enabled     Boost charge function is disabled	



# Interrupt 1 Status (02h)

Bits	Name	Description	Default Value
		Capacitor test complete indication bit.	
D[7]	CAP_TEST_DONE	1: The capacitor test is complete, and the discharge time is stored in the CAP_TEST_TIMER registers. This generates an interrupt on INT if unmasked. Write 1 to this bit to reset the interrupt event (and to reset this bit to 0)  0: A capacitor test event has not occurred	0
		Analog-to-digital (ADC) conversion complete indication bit.	
D[6]	ADC_DONE	1: ADC conversion is complete. This generates an interrupt on INT if unmasked. Write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: An ADC event has not occurred	0
		VIN to VB input current limit (I <sub>IN_LIMIT</sub> ) trigger indication bit.	
D[4]	INPUT_OVER_ CURRENT	1: V <sub>IN</sub> has triggered I <sub>IN_LIMIT</sub> . This generates an interrupt on INT if unmasked. Once the I <sub>IN_LIMIT</sub> event is removed, write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: An I <sub>IN_LIMIT</sub> event has not occurred	0
		Over-voltage (OV) on the OVP pin indication bit.	
D[3]	INPUT_OVER_ VOLTAGE	1: The OVP pin voltage ( $V_{\text{OVP}}$ ) has exceeded the OVP threshold ( $V_{\text{IN\_OVP}}$ ). This generates an interrupt on INT if unmasked. Once the over-voltage event is removed, write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: An OV event has not occurred	0
		Storage voltage (V <sub>STRG</sub> ) power not good indication bit.	
D[2]	PGS_NOT_OK	1: $V_{STRG}$ is below the PGS threshold. If the PGS pin detects that $V_{STRG}$ is too low, the device generates an interrupt on INT if unmasked. Once $V_{STRG}$ exceeds the PGS threshold, write 1 to this bit to reset the interrupt event (and to reset this bit to 0). PGS resets to high automatically once $V_{STRG}$ exceeds the PGS threshold 0: $V_{STRG}$ power has not dropped below the PGS threshold	1
		Temperature sensor high-voltage warning indication bit.	
D[0]	TEMP_WARN	1: The external temperature sensor on the TEMP pin has exceeded the TEMP_WARN level. This generates an interrupt on INT if unmasked. If a new ADC result from TEMP is below the threshold, write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: There is no TEMP_ADC result, or the TEMP_ADC result is below the TEMP_WARN level	0



# Interrupt 2 Status (03h)

Bits	Name	Description	Default Value
		SAS-forced buck mode indication bit.	
D[6]	SAS_DIS	1: The IC is disabled by the SAS signal, and forced into buck mode. This generates an interrupt on INT if unmasked. After SAS resets to low, write 1 to this bit to reset the interrupt event (and to reset this bit to 0)  0: A SAS force buck event has not occurred	0
		VIN to VB MOSFET is off indication bit.	
D[5]	ISOFET_OFF	1: The input isolation MOSFET is off. This generates an interrupt on INT if unmasked. Once the isolation MOSFET turns on again, write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: The isolation MOSFET is always on	1
		Thermal shutdown indication bit.	
D[4]	IC_TJ_ SHUTDOWN	1: The junction temperature (T <sub>J</sub> ) has exceeded 150°C. This generates an interrupt on INT if unmasked. After the temperature drops below 125°C, write 1 to this bit to reset the interrupt event (and to reset this bit to 0). The MP5514 resumes operation once T <sub>J</sub> drops, even if the interrupt signal is not cleared 0: Thermal shutdown has not occurred	0
		High temperature warning bit.	
D[3]	IC_TJ_WARN	1: T <sub>J</sub> has exceeded 125°C. This generates an interrupt on INT if unmasked. Once T <sub>J</sub> drops below 100°C, write 1 to this bit to reset the interrupt event (and to reset this bit to 0) 0: T <sub>J</sub> has not exceeded 125°C; a high temperature warning has not occurred	0



# Interrupt 1 Mask Control (04h)

Bits	Name	Description	Default Value
D[7]	CAP_TEST_ DONE_MASK	Capacitor test complete interrupt mask.  1: The CAP_TEST_DONE interrupt is masked. The CAP_TEST_DONE status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The CAP_TEST_DONE interrupt is not masked	0
D[6]	ADC_DONE_MASK	ADC complete interrupt mask.  1: The ADC_DONE interrupt is masked. The ADC_DONE status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The ADC_DONE interrupt is not masked	0
D[4]	INPUT_OVER_ CURRENT_MASK	VIN to VB I <sub>IN_LIMIT</sub> interrupt mask.  1: The INPUT_OVER_CURRENT interrupt is masked. The INPUT_OVER_CURRENT status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The INPUT_OVER_CURRENT interrupt is not masked	0
D[3]	INPUT_OVER_ VOLTAGE_MASK	OVP interrupt mask.  1: The INPUT_OVER_VOLTAGE interrupt is masked. The INPUT_OVER_VOLTAGE status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: INPUT_OVER_VOLTAGE is not masked	0
D[2]	PGS_NOT_ OK_MASK	PGS power not good interrupt mask.  1: The PGS_NOT_OK interrupt is masked. The PGS_NOT_OK status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The PGS_NOT_OK interrupt is not masked	1
D[0]	TEMP_ WARN_MASK	Temperature sensor high-voltage warning interrupt mask.  1: The TEMP_WARN interrupt is masked. The TEMP_WARN status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The TEMP_WARN interrupt is not masked	0



# Interrupt 2 Mask Control (05h)

Access: Read/Write

Bits	Name	Description	Default Value
D[6]	SAS_DIS_MASK	SAS force buck event interrupt mask.  1: The SAS_DIS interrupt is masked. The SAS_DIS status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The SAS_DIS interrupt is not masked	0
D[5]	ISOFET_OFF_MASK	Isolation MOSFET off event interrupt mask.  1: The ISOFET_OFF interrupt is masked. The ISOFET_OFF status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The ISOFET_OFF interrupt is not masked	1
D[4]	IC_TJ_ SHUTDOWN_MASK	OTP interrupt mask.  1: The IC_TJ_SHUTDOWN interrupt is not masked. The IC_TJ_SHUTDOWN status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The IC_TJ_SHUTDOWN interrupt is not masked	0
D[3]	IC_TJ_WARN_MASK	High temperature warning interrupt mask.  1: The IC_TJ_WARN interrupt is masked. The IC_TJ_WARN status bit is set after an interrupt event, but this bit suppresses the interrupt signal on INT  0: The IC_TJ_WARN interrupt is not masked	0

# **Backup Capacitor Threshold (06h)**

Bits	Name	Description	Default Value
DIZI	EDG LIVG	Boost refresh threshold. When FBS drops to V <sub>FBS_REF</sub> , PLP starts switching and charges V <sub>FBS</sub> to V <sub>FBS_REF</sub> + FBS_HYS.	0
D[7]	FBS_HYS	0: 9mV (typically), 13.5mV max 1: 10mV (typically), 15mV max	0
		V <sub>IN</sub> recovery mode.	
D[6]	VIN_RECOVER_ MODE	O: The part operates in buck release mode until V <sub>BUS</sub> drops below V <sub>BUS_UVLO</sub> once V <sub>IN</sub> recovers  1: The part exits buck release mode and charges V <sub>S</sub> once V <sub>IN</sub> recovers	0
D[5:4]	ICH	Sets the peak boost switching current limit while ICH is floating.  00: 0.5A  01: 1A  10: 1.5A  11: 2A	11
D[3:0]	PGS_THRESHOLD	Configurable PGS falling threshold, with a 1% step 0000: 80% of V <sub>FBS_REF</sub> 1111: 95% of V <sub>FBS_REF</sub>	1111



# **Temperature Warning Threshold (07h)**

Access: Read/Write

Bits	Name	Description	Default Value
	EFUSE_UVLO	E-fuse UVLO threshold. These bits are assigned to the OTP pin. After cycling the power, the UVLO rising and falling threshold are set to the OTP value.	
D[7:6]		00: The UVLO rising threshold is 2.5V, and the falling threshold is 2.3V 01: The UVLO rising threshold is 3.7V, and the falling threshold is 3.4V 10: The UVLO rising threshold is 7.2V, and the falling threshold is 3.4V 11: The UVLO rising threshold is 9.5V, and the falling threshold is 3.4V	11
		Backup buck converter over-current (OC) response.	
D[5]		0: PLP enters buck release mode only if DET is triggered.     1: PLP enters buck release mode if DET is triggered or EFUSE_OC and FBB drop below V <sub>FBB_REF</sub>	0
D[4:0]	TEMP_ADC_ WARN_ LEVEL	Sets the warning level for the TEMP pin voltage ADC results (from external sensor). The TEMP_ADC results high bits are compared to this warning level.	11111

## **Reverse Current Fast-Off (08h)**

Access: Read/Write

Bits	Name	Description	Default Value
D[7]	REVERSE_ CURRENT_FAST_ OFF_DISABLE	Enables the reverse-current fast-off function.  0: The reverse-current fast-off function is enabled  1: The reverse-current fast-off function is disabled	0

# **ADC Source Select (09h)**

Bits	Name	Description	Default Value
D[4]	BACKUP_VOLTAGE	Enables the V <sub>STRG</sub> ADC conversion.  1: V <sub>STRG</sub> ADC conversion is enabled  0: V <sub>STRG</sub> ADC conversion is disabled	0
D[2]	TEMP_PIN	Enables the temperature sensor voltage ADC conversion.  1: Temperature sensor voltage ADC conversion is enabled 0: Temperature sensor voltage ADC conversion is disabled	0
D[1]	INPUT_CURRENT	Enables the input current signal ADC conversion. The input current (I <sub>IN</sub> ) is monitored via the ILIM pin. If the current triggers the I <sub>IN</sub> limit (I <sub>IN_LIMIT</sub> ), then the ILIM voltage (V <sub>ILIM</sub> ) is 1.09V. Calculate the current based on the ILIM resistor (R <sub>ILIM</sub> ) setting.  1: I <sub>IN</sub> signal ADC conversion is enabled 0: I <sub>IN</sub> signal ADC conversion is disabled	0
D[0]	INPUT_VOLTAGE	Enables the V <sub>IN</sub> ADC conversion.  1: V <sub>IN</sub> ADC conversion is enabled  0: V <sub>IN</sub> ADC conversion is disabled	0



# ADC Results (0Ah, 0Bh, 0Ch, 0Dh, 0Eh, 0Fh, 12h, 13h, 14h, and 15h)

Access: Read-Only

Bits	Name	Description	Default Value
0Ah, D[7:0]	ADC_INPUT_	High bits of the V <sub>IN</sub> ADC results.	0000 0000
0Bh, D[1:0]	VOLTAGE_DATA	Low bits of the $V_{IN}$ ADC results. LSB = $18.4 / 1023(V)$	00
0Ch, D[7:0]		High bits of the I <sub>IN</sub> ADC results.	0000 0000
0Dh, D[1:0]	ADC_INPUT_ CURRENT_DATA	Low bits of the I <sub>IN</sub> ADC results. $V\_LSB = 1.28 \ / \ 1023 \ (V)$ $IN = V\_LSB \ x \ BIN2DEC(D[9:0]) \ x \ 64.26 \ / \ R_{ILIM} + 0.241 \ / \ R_{ILIM} + 0.08(A)$ Where $R_{ILIM}$ is in $k\Omega$ .	00
0Eh D[7:0]	High bits of the temperature sensor voltage ADC results.  ADC_TEMP_		0000 0000
0Fh D[1:0]	VOLTAGE_DATA	Low bits of the temperature sensor voltage ADC results.  LSB = 1.28 / 1023 (V)	00
12h, D[7:0]	ADC_BACKUP_	High bits of the V <sub>STRG</sub> ADC1 results.	0000 0000
13h, D[1:0]	VOLTAGE_DATA1	Low bits of the V <sub>STRG</sub> ADC1 results.  LSB = 40.1 / 1023 (V)	00
14h D[7:0]	ADC_BACKUP_	High bits of backup storage voltage ADC2 results.	0000 0000
15h D[1:0]	VOLTAGE_DATA2	Low bits of the $V_{STRG}$ ADC2 results. LSB = $40.1 / 1023$ (V)	00

# Capacitor Test Timer (16h and 17h)

Access: Read-Only

Bits	Name	Description	Default Value
16h, D[7:0]	CAP_TEST_	Low bits of the capacitor test timer results.  LSB = 1ms	0000 0000
17h, D[7:0]	TIMER	High bits of the capacitor test timer results.	0000 0000



# **VIN Recover Control (1Bh)**

Access: Read/Write

Bits	Name	Description	Default Value
		0: Disables the LDO from STRG to VCC. 1: Enables the LDO from STRG to VCC.	
D[1]	D[1] LDO_EN	It is recommended to only enable the LDO during the ADC or capacitor test if both $V_{\text{IN}}$ and $V_{\text{BUS}}$ are below 3.8V. Disable the LDO_EN bit after the ADC or capacitor test is complete.	0

# System Control 2 (20h)

Access: Read/Write

Bits	Name	Description	Default Value
D[6]	INPUT_ILIM_SET	This bit determines how I <sub>IN_LIMIT</sub> is set.  1: I <sub>IN_LIMIT</sub> is set by the internal circuit  0: I <sub>IN_LIMIT</sub> is set by the external R <sub>ILIM</sub>	0
D[3:1]	BUCK_FSW	These bits set the buck switching frequency (f <sub>SW</sub> ).  000: 270kHz 001: 300kHz 010: 360kHz 011: 420kHz 100: 480kHz 101: 570kHz 110: 860kHz 111: 1.25MHz	100
D[0]	FORCE_BUCK_ RELEASE	This bit forces the IC to operate in buck release mode. Once this bit is reset to 0, the MP5514 remains in buck release mode until V <sub>BUS</sub> drops below V <sub>BUS_UVLO</sub> .  0: No action 1: The IC is forced to enter buck release mode	0



# System Control 3 (21h)

Access: Read/Write

Bits	Name	Description	Default Value
D[7:5]	INTERNAL_ILIM_ THRESHOLD	These bits set the internal I <sub>IN_LIMIT</sub> threshold.  000: 6.6A 001: 5.6A 010: 2.3A 011: 2.3A 100: 2.3A 101: 1.3A 110: 4.7A 111: 3.4A	000
D[4:3]	DVDT	These bits set the V <sub>BUS</sub> slew rate.  00: 7.5V/ms 01:1.5V/ms 10: 1V/ms 11: 0.67V/ms	00
D[2:1]	TPOR	These bits set the TPOR delay time while the TPOR pin is floating.  00: 1.6ms 01: 8ms 10: 32ms 11: 64ms	00
D[0]	EN	This bit enables the device. The EN bit is not writable during buck release mode unless until V <sub>BUS</sub> drops below V <sub>BUS_UVLO</sub> .  0: The MP5514 is disabled 1: The MP5514 is enabled	1

# System Control 4 (22h)

Access: Read/Write

Bits	Name	Description	Default Value
D[3]	ILIM_EN	This bit enables the isolation MOSFET current limit (ILIMIT).  0: The isolation MOSFET ILIMIT is enabled  1: The isolation MOSFET ILIMIT is disabled (ILIMIT can be disabled while the input OC limit status bit is set)	0
D[2:0]	ILIM_TUNE	These bits tune I <sub>IN_LIMIT</sub> .  000: Keeps I <sub>IN_LIMIT</sub> set at 100%  001: Decreases I <sub>IN_LIMIT</sub> by 2%  010: Increases I <sub>IN_LIMIT</sub> by 2%  011: Decreases I <sub>IN_LIMIT</sub> by 4%  100: Increases I <sub>IN_LIMIT</sub> by 4%	000



# SAS\_CTRL (26h)

Access: Read-only

Bits	Name	Description	Default Value
D[7]	I2C_TO_EN	I <sup>2</sup> C reset.  0: I <sup>2</sup> C does not reset after the timeout time  1: I <sup>2</sup> C resets if SCL is pulled low or high for up to 25ms, or if SDA is pulled low for up to 450ms	1
D[6]	SAS_DLY	During start-up, the SAS input is ignored for the first interval set by this bit. After a reset is complete, the value changes to the set OTP value.  0: 0s 1: 30s	1
D[5:4]	SAS_ASSERT_TIME	To assert SAS signal, hold the SAS high for longer than SAS_ASSERT_TIME. After a reset is complete, changes to the set OTP value.  00: No hold time 01:1s 10: 5s 11: 10s	10
D[3:2]	SAS_NEGATE_TIME	To negate the SAS signal, hold the SAS pin low for longer than SAS_NEGATE_TIME. After a reset is complete, changes to the set OTP value.  00: No hold time 01: 1s 10: 10s 11: 30s	11



## APPLICATION INFORMATION

## **Setting the Storage Voltage**

V<sub>STRG</sub> is set by the external feedback (FB) resistors R5 and R6 (see Figure 13).

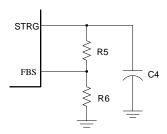


Figure 13: Storage Feedback Circuit

V<sub>STRG</sub> can be calculated with Equation (8):

$$V_{STRG} = (1 + \frac{R5}{R6}) \times V_{FBS\_REF}$$
 (8)

Where V<sub>FBS</sub> <sub>REF</sub> is typically 0.8V.

R5 and R6 are not critical for normal operation. Choose R6 to be between  $10k\Omega$  and  $50k\Omega$  to reduce the bleed current and improve noise immunity. For example, if R6 is  $10k\Omega$ , then R5 can be calculated with Equation (9):

$$R5 = \frac{10k\Omega \times (V_{STRG} - V_{FBS\_REF})}{V_{FBS\_REF}}$$
 (9)

For a 30V  $V_{STRG}$ , R5 should be 365k $\Omega$ .

Table 3 lists the recommended R5 and R6 resistances for different storage voltages.

Table 3: R5 and R6 Resistances for Different Storage Voltages

V <sub>STRG</sub> (V)	R5 (kΩ)	R6 (kΩ)
12	140	10
20	240	10
30	365	10

# Setting the V<sub>IN</sub> Power Failure Threshold Voltage and Bus Release Regulation Voltage

The release trigger voltage is set by the external FB resistors R1 and R2 (see Figure 14).

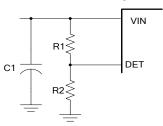


Figure 14: Release Feedback Circuit

The release trigger voltage is determined by  $(0.99 \times V_{DET REF})$ , which is 0.792V.

The input power failure release threshold (V<sub>PFI</sub>) can be calculated with Equation (10):

$$V_{PFI} = (1 + \frac{R1}{R2}) \times 0.792V \tag{10}$$

 $V_{DET}$  determines the release trigger voltage, and  $V_{FBB}$  determines  $V_{BUS\ RLS}$  (see Figure 15).

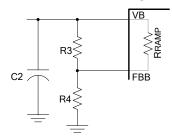


Figure 15: VB Regulation Feedback Circuit

The bus regulation voltage ( $V_{BUS\_RLS}$ ) can be calculated with Equation (11):

$$V_{BUS\_RLS} = (1 + \frac{R3//R_{RAMP}}{R4}) \times V_{FBB\_REF}$$
 (11)

Where  $V_{\text{FBB\_REF}}$  is typically 0.8V, and  $R_{\text{RAMP}}$  is an equivalent resistor that stabilizes the circuit internally (typically  $9M\Omega$ ).

R3 and R4 are related to the buck release stability. Since release buck mode works during constant-on-time (COT) control, avoid using smaller resistor values that can affect the internal voltage ramp. Choose R3 to be parallel to R4. R3 and R4 should exceed  $10k\Omega$  for stable performance with a  $C_{BUS}$  between  $22\mu F$  and  $44\mu F$ .

## **Selecting the Storage Capacitor**

 $C_{\rm STRG}$  stores energy during normal operation and releases this energy to VB once VIN loses input power. Use a general-purpose electrolytic capacitor or low-profile POSCAP for most applications. Select a  $C_{\rm STRG}$  with a voltage margin 20% above the targeted  $V_{\rm STRG}$ . When choosing the capacitors, consider the capacitance reduction with the DC voltage offset. Different capacitors have different capacitance derating performances. Choose a capacitor with a voltage rating large enough to guarantee enough capacitance.

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The required C<sub>STRG</sub> depends on the length of the dying gasp (t<sub>DASP</sub>) for a typical application. The required C<sub>STRG</sub> can be calculated with Equation (12):

$$C_{STRG} = \frac{2 \times V_{BUS\_RLS} \times I_{RELEASE} \times t_{DASP}}{(V_{STRG}^2 - V_{BUS\_RLS}^2) \times Eff}$$
 (12)

Where IRELEASE is the bus release current when V<sub>BUS</sub> is regulated at V<sub>BUS</sub> R<sub>LS</sub> for the DC/DC converter, t<sub>DASP</sub> is the required dying gasp time, Eff is the buck converter's energy release efficiency (see the Buck Efficiency curves on page 15 for more details).

Choose a C<sub>STRG</sub> that ensures enough capacitance for buck power loss. If IRELEASE is 3A, t<sub>DASP</sub> is 20ms, V<sub>STRG</sub> is 28V, V<sub>BUS RLS</sub> is 7.5V, and the efficiency is 90%, then  $C_{STRG}$  should be 1374µF.

## **Setting the Input Hot-Swap Current Limit**

Connect a resistor between the ILIM and AGND pins to set I<sub>IN LIMIT</sub>. For example, if the ILIM resistor (R<sub>ILIM</sub>), then I<sub>IN LIMIT</sub> is set to about 2A. See to the Input Current Limit section on page 20 for more details.

The MP5514 also supports an internal ILIM configuration function, which can be set by the INPUT ILIM SET and INTERNAL ILIM THRESHOLD register bits via the I<sup>2</sup>C interface. See the INPUT ILIM SET register description on INTERNAL\_ILIM\_ page 38 and the THRESHOLD register description on page 39 for more details.

## **Setting the Boost Peak Current Limit**

Connect a resistor between the ICH and AGND pins to set the boost peak ILIMIT. See the Storage Voltage section on page 19 for more details.

Float the ICH pin to configure the boost peak I<sub>LIMIT</sub> via the ICH register bits. The boost peak current is about 2A, with a default register value of 11 (under typical conditions where  $V_{IN} = 12V$ and  $L = 10\mu H$ ).

#### Selecting the Inductor

An inductor is required for supplying constant current to the load. Since boost charge mode and buck release mode share the same inductor (and the buck mode current is typically larger), it is recommended to choose an inductor that supports the buck release mode current.

If the buck is operating at a fixed frequency (480kHz), then the inductance (L) can be calculated with Equation (13):

$$L = \frac{V_{BUS\_RLS}}{\Delta I_{L} \times f_{SW}} \times (1 - \frac{V_{BUS\_RLS}}{V_{STRG}})$$
 (13)

Where  $\Delta I_{\perp}$  is the peak-to-peak inductor ripple current, which can be set between 20% and 40% of the full release current.

The inductor should not saturate under the maximum peak I<sub>L</sub>.

## Setting the Start-Up Reset Delay Time

Connect a ≥1nF TPOR capacitor (C<sub>TPOR</sub>) to the TPOR pin to set t<sub>TPOR</sub>. Float C<sub>TPOR</sub> for the default delay time (about 1.5ms). Table 4 lists the recommended capacitances for different delay times.

Table 4: TPOR Capacitances for Different t<sub>TPOR</sub>

t <sub>TPOR</sub> (ms)	C <sub>TPOR</sub> (nF)
10	10
100	100
500	500

## Setting the Bus Voltage Rise Time

Connect a ≥1nF capacitor to DVDT to set the bus voltage start-up slew rate and tss. Float this capacitor for the default soft-start slew rate (about 7.5V/ms, and 1.6ms from 0V to 12V). Table 5 lists the recommended capacitors for different soft-start slew rates.

Table 5: Capacitor Values for Different Soft-Start Slew Rates

Soft-Start Slew Rate (V/ms)	C <sub>DV/DT</sub> (nF)		
3.9	10		
0.39	100		

## **Recommended ADC Input Range**

The MP5514 ADC V<sub>IN</sub> is between 0V to 1.28V. To improve ADC monitoring accuracy, it is recommended to set the target monitor voltage between 0.64V and 1.28V (i.e. in the front half of the ADC V<sub>IN</sub> range). If a wider V<sub>IN</sub> range is necessary, do not set the ADC V<sub>IN</sub> below 0.1V to avoid errors.

The TEMP pin is used as the temperature-sense input from the thermistor to the ADC.



Do not use the ADC when the TEMP pin voltage is below 0.1V.

## **VCC Power Supply**

VCC is powered by the VIN pin during start-up. An external load on VCC is not permitted. If the PFI and INT signals are pulled up to VCC while  $V_{IN}$  is below 3V, use  $100k\Omega$  resistors to decrease the VCC sink current during start-up.

The MP5514 can start up from a 2.7V  $V_{IN}$  at temperatures  $\geq$ 25°C. If the temperature is below 25°C, then the UVLO point increases slightly. Connect an external Schottky diode between VIN and VCC if the IC should to start up with a 2.7V  $V_{IN}$  at low temperatures. This diode is recommended even if  $V_{IN}$  is 3V at -40°C).

# Selecting the Bootstrap (BST) and CST Capacitors

The bootstrap (BST) capacitor ( $C_{BST}$ ) supplies power to the buck converter's HS-FET. A 0.1 $\mu$ F to 1 $\mu$ F ceramic capacitor is recommended for BST decoupling.  $C_{CST}$  supplies power to the input hot-swap MOSFET and the VBO disconnect MOSFET.  $C_{CST}$  is charged by an internal charge pump.  $C_{CST}$  should be below 47nF, as it can affect the voltage charge-up slew rate. A 10nF ceramic capacitor is recommended for  $C_{CST}$ .

## **Storage Capacitor Test Resistor**

The MP5514 discharges  $C_{STRG}$  via an external resistor between the STRG and RTEST pins. The MOSFET between RTEST and GND is about 4.5 $\Omega$ , and the discharge peak current should be limited below 500mA by an external resistor. Consider the resistance if the selected RTEST resistance ( $R_{RTEST}$ ) is close to 4.5 $\Omega$ . Typically, a 1k $\Omega$  to 10k $\Omega$  discharge resistor is recommended to reduce the resistor's size. Other resistor values are also sufficient.

## **Selecting the Input Capacitor and TVS Diode**

VIN capacitors are recommended to absorb voltage spikes at the input during start-up, input switching hard-off (during shutdown), or other conditions. The application determines the capacitance required. For example, if the input power trace is too long (and has a higher parasitic inductance) during the input-switch hard-off period, then more energy is pumped into the input. This means that more input capacitors are required to reduce the  $V_{\text{IN}}$  spike and remain within the safe operating range. A  $0.1\mu\text{F}$  or larger input capacitor ( $C_{\text{IN}}$ ) is recommended.

Consider the application inrush current requirements when selecting C<sub>IN</sub>. Typically, more input capacitors result in a higher inputinrush current during hot-plugging. A smaller C<sub>IN</sub> is required for a smaller inrush current. The MP5514 can operate normally with a very small C<sub>IN</sub> or without any input capacitance; however, this may lead to high voltage spikes. An efficient solution is to add a TVS diode at the input to absorb the possible V<sub>IN</sub> spike. This also keeps the inrush current small during hot-plugging. A typical TVS diode (e.g. SMA6J13A) V<sub>BUS RLS</sub>, is recommended.

#### **Design Example**

Table 6 is a design example following the application guidelines for the following specifications.

**Table 6: Design Example** 

V <sub>IN</sub>	12V		
V <sub>STRG</sub>	30V		
$V_{PFI}$	8V		
V <sub>BUS_RLS</sub>	7.5V		
I <sub>RELEASE</sub>	5A		

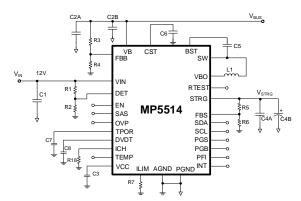
Figure 17 on page 45 shows a typical application circuit. For more device applications, refer to the related evaluation board datasheet.



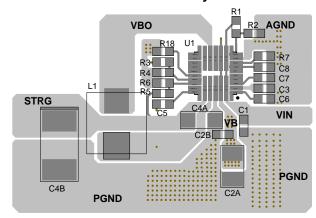
## **PCB Layout Guidelines**

Efficient PCB layout is critical for stable operation. For the best results, refer to Figure 16, and follow the guidelines below.

- 1. Connect the high-current paths (VIN, VB, VBO, SW, STRG, and PGND) using short, wide, and direct traces.
- 2. Keep the SW trace as short as possible.
- 3. Route the VBO trace away from SW.
- 4. Place the decoupling capacitor between VB and PGND. Place this capacitor as close to VB and PGND as possible.
- 5. Place the decoupling capacitor between STRG and PGND. Place this capacitor as close STRG and PGND as possible. If using a larger-value capacitor, a small ≥1µF ceramic capacitor is required. Place this small capacitor as close to STRG and PGND as possible.
- 6. Place the decoupling capacitor between VCC and AGND. Place this capacitor as close to VCC and AGND as possible.
- 7. Keep the switching node SW short and away from the feedback network.
- 8. Place the external feedback resistors near FBB, FBS, and DET.
- 9. Keep the BST voltage path (BST, C5 and SW) as short as possible.
- 10. Connect all of the signal grounds together at PGND with a one-point connection.



#### Schematic for Layout



**Top Layer** 

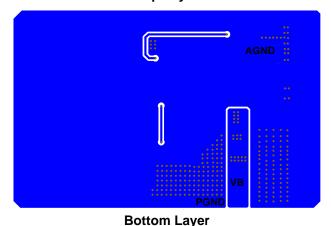


Figure 16: Recommended PCB Layout



# **TYPICAL APPLICATION CIRCUITS**

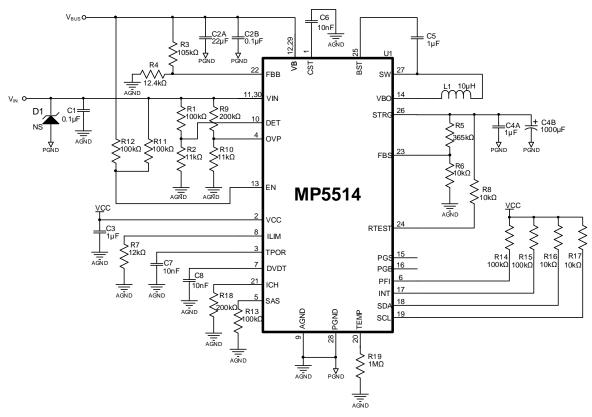
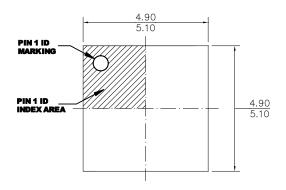


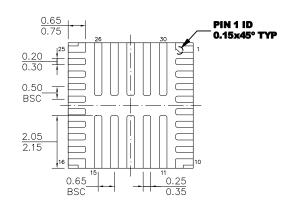
Figure 17: Typical Application Circuit (12V Input, 30V Storage)



# **PACKAGE INFORMATION**

# **QFN-30 (5mmx5mm)**



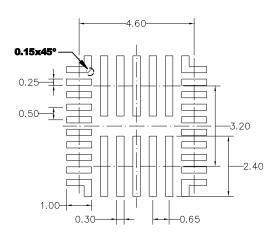


## **TOP VIEW**

**BOTTOM VIEW** 



## **SIDE VIEW**



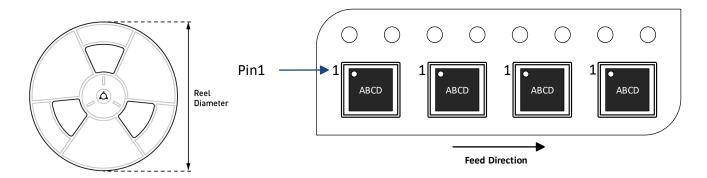
**RECOMMENDED LAND PATTERN** 

## **NOTE:**

- 1) ALL DIMENSIONS ARE IN MILLIMETERS.
- 2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
- 3) LEAD COPLANARITY SHALL BE 0.10 MILLIMETERS MAX.
- 4) REFERENCEIS MO-220.
- 5) DRAWING IS NOT TO SCALE.



# **CARRIER INFORMATION**



Part Number	Package	Quantity/	Quantity/	Quantity/	Reel	Carrier	Carrier
	Description	Reel	Tube	Tray	Diameter	Tape Width	Tape Pitch
MP5514GU- xxxx-Z	QFN-30 (5mmx5mm)	5000	N/A	N/A	13in	12mm	8mm



# **REVISION HISTORY**

Revision #	Revision Date	Description	Pages Updated
1.0	2/16/2023	Initial Release	-
1.1	7/18/2024	Updated part number in Ordering Information section to "MP5514GU-xxxx"; updated MSL Rating to 1	3
		Updated part number in Carrier Information section to "MP5514GU-xxxx-Z"	47

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